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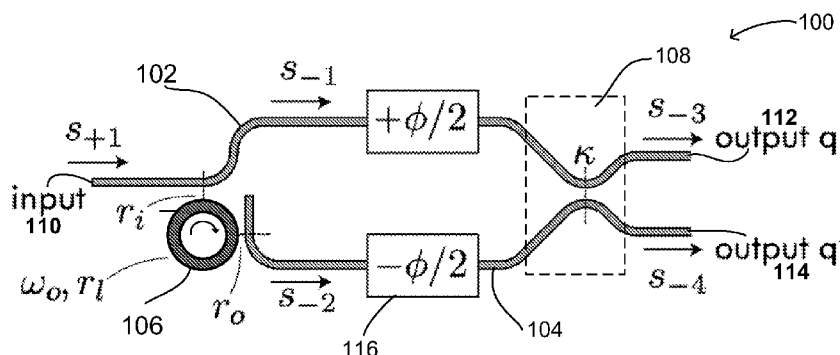


FIG. 1B

(57) Abstract: Disclosed are optical modulators that have two coupling paths or structures between an input port to an output port, at least one of which includes an optical resonator.

RESONANT OPTICAL MODULATORS

CROSS-REFERENCE TO RELATED APPLICATION

[0001] This application claims priority to and the benefit of U.S. Provisional Patent Application No. 61/119,622, filed December 3, 2008, which is hereby incorporated herein by reference in its entirety.

STATEMENT REGARDING FEDERALLY

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SPONSORED RESEARCH OR DEVELOPMENT

[0002] The U.S. Government has a paid-up license in this invention and the right in limited circumstances to require the patent owner to license others on reasonable terms as provided for by the terms of Grant No. W911NF-08-1-0362 awarded by the U.S. Army Research Office.

TECHNICAL FIELD

10 [0003] The present invention relates, in various embodiments, to optical modulators and, more particularly, to resonator-based modulators with improved transfer properties between input and output ports.

BACKGROUND

[0004] Optical intensity modulators are important devices for optical communication, i.e.,
15 for imparting information onto laser light. They typically have the ability to modulate the intensity of an incident narrow-line (continuous-wave) laser signal from close to 100% of its nominal maximum value to close to 0%. In wavelength-division-multiplexed (WDM) systems, a modulator is typically needed for each wavelength, so it is desirable to have wavelength-selective modulators that can be cascaded, such that each is able to modulate a select
20 wavelength without affecting other wavelengths. Preferably, such modulators can be integrated on a chip in large numbers, to scale with large numbers of wavelengths used. Therefore, modulators should also be small and energy-efficient. Energy-efficiency is particularly important for on-chip optical interconnects for multi-core microprocessors, and for on-chip optical transmitters on microprocessors as part of either all-on-chip or part-on-chip/part-off-
25 chip optical networks between processors and/or between processors and memory. Finally, there are applications where a modulator with two output ports is employed to provide the

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modulated output signal (e.g., 1000101) in one port, and the complementary signal (i.e., 0111010) in the other port.

[0005] In general, modulators are designed to: (i) maximize modulation speed; (ii) minimize the energy required to modulate; (iii) minimize the optical bandwidth occupied by the modulation in order to allow cascading of modulators without crosstalk and with minimal wavelength spacing; and (iv) minimize the driving signal (to avoid material breakdown or to be able to use typical voltage levels available with CMOS driving circuits, on the order of 1V to 5V), which simultaneously aids in minimizing the energy required to modulate. In general, there is a trade-off between achieving these goals – in particular (i) and (ii), usually referred to as the sensitivity-bandwidth trade-off. Achieving high-speed modulation calls for photon lifetimes shorter than the modulation period, and is associated with a broad modulation bandwidth requiring strong actuation signals (e.g., voltages or currents). On the other hand, high sensitivity of the modulation to the driving signal typically requires sharp amplitude changes within a narrow optical bandwidth range of the device. Then, weak spectral shifting in the spectral response caused by weak modulation may be sufficient to substantially shift the sharp spectral feature across the fixed-wavelength input wave. Consequently, there is a limit to simultaneously achieving high speed and high sensitivity.

[0006] Energy-efficient modulators may be optically resonant structures, such as silicon microring resonators coupled to a waveguide, or Mach-Zehnder interferometers assisted by a ring resonator in at least one of the interferometer arms. Such modulators have a number of drawbacks. Structures using a cavity coupled to a waveguide have a Lorentzian response, which means that even when they are loss-less, i.e., have 100% transmission on resonance to the drop port, they do not roll off to a full zero transmission off resonance. As a result, they typically require that the resonance be moved during modulation by more than one bandwidth in order to achieve practically low transmission (that gives large on-to-off contrast, i.e., extinction ratio), which is energetically costly. Further, the extinction ratio of these devices may deteriorate when loss is associated with the frequency shift during modulation. This is the case, for example, when modulation is achieved with carrier injection in silicon, i.e., using the carrier-plasma effect. Modulators using a ring-loaded Mach-Zehnder configuration have the drawback of using multiple 3dB splitters, which typically cause substantial losses on resonance. This is because a 3dB splitter is difficult to design and realize to be lossless, and, furthermore, symmetric splitters approaching 50%:50% splitting (3dB) have higher losses in general than asymmetric splitters with weak splitting approaching 0%:100%. Namely, the loss is typically

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considerably smaller than the smaller of the two output fractions. Furthermore, such modulator devices may have 3dB loss off resonance at all wavelengths and may, therefore, be unsuitable for direct cascading in a WDM system.

[0007] Accordingly, a need exists for an improved resonant optical modulator.

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SUMMARY

[0008] The present invention provides, in various embodiments, resonator-based optical modulators that are designed to improve modulation performance parameters, such as, for example, modulation speed, sensitivity, and/or energy-efficiency, and/or allow for modulator cascading. In general, the modulators include a first waveguide providing an input port and a first output (or through) port, a second waveguide providing a second output (or drop) port, and two coupling structures between the two waveguides. One of the coupling structures is an “optically active resonator,” which, for purposes of this disclosure, denotes an optical resonator having a variable resonance frequency and/or a variable absorption coefficient that facilitate continuous optical modulation of an input signal between a first modulation state and a second modulation state.

[0009] The modulation performance of the device may be improved or optimized by engineering the transfer functions between the input and output ports by exploiting various degrees of freedom of the device, such as design parameters of the two coupling structures (e.g., coupling strengths, resonance frequency or frequencies of the modulator, etc.) and/or of optional additional device components (e.g., phase shifts induced by optical phase shifters). For example, the transfer functions may be designed such that one of the output ports has a transmission zero at the signal wavelength in the first modulation state, and the other output port has a transmission zero at the signal wavelength in the second modulation state.

[0010] The waveguides and resonator are typically strong-confinement devices, i.e., structures capable of confining, and optionally enhancing, an optical-regime electromagnetic field within a space on the scale of a few wavelengths, preferably less than a wavelength, in at least one dimension, preferably in two or in all three dimensions (in an arbitrary coordinate system of choice). For example, a channel waveguide, as used in various embodiments, confines optical fields in two dimensions, and a cavity resonator confines optical fields in three dimensions. Strong confinement may be achieved using high index contrast between the confining structures and the surrounding material (e.g., air or cladding material). The optical regime, as used herein, denotes a range of frequencies larger than 1 THz (corresponding to

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wavelengths shorter than 300 μm in the THz-wave regime) and smaller than 3000 THz (corresponding to wavelengths longer than 100 nm in the UV regime).

[0011] In a first aspect, embodiments of an optical modulator in accordance with the invention feature first and second optical waveguides, the first waveguide including an input port and a through port and the second waveguide including a drop port; as well as an optical resonator and a coupling structure, both optically coupled to each of the two waveguides. In some embodiments, the optical resonator is located in a first layer of the modulator, and the waveguides and coupling structure are located in a second layer. A transfer function from the input port to the through port may have a transmission zero at a frequency of the input signal in a first modulation state, and a transfer function from the input port to the drop port may have a transmission zero at the frequency of the input signal in a second modulation state.

[0012] The optical resonator may be optically active, and may include a microring resonator, a figure-eight resonator, a standing-wave cavity pair, and/or a photonic cavity pair. The coupling structure may include a directional coupler (which may couple, for example, between 13% and 87% of the input signal from the first to the second optical waveguide), a waveguide junction and/or multimode interference coupler joining the first and second waveguides, and/or a second optical resonator. In certain embodiments, the first optical resonator forms part of the coupling structure. In some embodiments, the first optical resonator and a second optical resonator that forms part of the coupling structure are each directly coupled to the first waveguide, and indirectly, via one or more additional optical resonators, to the second waveguide. The optical modulator may further include a phase shifter in one or each of the waveguides between the first optical resonator and the coupling structure, and the phase shifter(s) may induce a differential phase shift between the two waveguides. The differential phase shift may be substantially equal to the inverse tangent of a ratio of an absorption detuning to a frequency detuning associated with modulation from a first modulation state to a second modulation state.

[0013] In a second aspect, an optical modulator in accordance with various embodiments includes an optical input port for receiving an input signal, optical through and drop ports, and an optical resonator structure coupling the input port to the through port and the drop port, and is characterized by a transfer function from the input port to the through port having a transmission zero at a frequency of the input signal in a first modulation state and a transfer function from the input port to the drop port having a transmission zero at the signal frequency in a second modulation state. The modulation from the first state to the second state may be

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associated with a frequency detuning and an absorption detuning, and a differential phase shift between the through and drop ports may be substantially equal to the inverse tangent of the absorption detuning to the frequency detuning. In some embodiments, the optical resonator structure includes a plurality of optical resonators.

5 [0014] In a third aspect, the invention is directed to a wavelength-selective optical modulator which includes optical input and output ports, a first path connecting the input port to the output port and including at least two optical resonators, and a second path connecting the input port to the output port via a structure outside of the first path. In some embodiments, at least one of the optical resonators is modulated, and at least one of the optical resonators is
10 passive. In certain embodiments, a transfer function from the input port to the output port has a first transmission zero at a complex-frequency detuning from a resonance of less than three 3dB bandwidths and a second transmission zero at a complex-frequency detuning from the resonance of more than six 3dB bandwidths.

[0015] These and other objects, along with advantages and features of the embodiments of
15 the present invention herein disclosed, will become more apparent through reference to the following description, the accompanying drawings, and the claims. Furthermore, it is to be understood that the features of the various embodiments described herein are not mutually exclusive and can exist in various combinations and permutations.

BRIEF DESCRIPTION OF THE DRAWINGS

20 [0016] In the drawings, like reference characters generally refer to the same parts throughout the different views. Also, the drawings are not necessarily to scale, emphasis instead generally being placed upon illustrating the principles of the invention. In the following description, various embodiments of the present invention are described with reference to the following drawings, in which:

25 [0017] FIG. 1A is a drawing illustrating conceptually a first-order resonant modulator in accordance with various embodiments;

[0018] FIG. 1B is a drawing illustrating schematically an implementation of a first-order modulator including a microring resonator and directional coupler in accordance with one embodiment;

30 [0019] FIGS. 2A and 2B are graphs showing transfer functions of the modulator depicted in FIG. 1B in the through port and drop port, respectively, for several values of the coupling power ratio of the directional coupler in accordance with one embodiment;

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[0020] FIG. 3 is a pole-zero plot for a first-order resonant modulator in accordance with various embodiments;

[0021] FIGS. 4A and 4B are graphs showing the transfer functions of the modulator depicted in FIG. 1B in the through port and drop port, respectively, for several levels of refractive-index modulation in accordance with one embodiment;

[0022] FIG. 4C is a pole-zero plot illustrating refractive-index modulation of the modulator depicted in FIG. 1B in accordance with one embodiment;

[0023] FIG. 4D is a graph illustrating the power transmission in the through port of the modulator depicted in FIG. 1B as a function of the level of refractive-index modulation in accordance with one embodiment;

[0024] FIG. 5 is a graph illustrating transmission zero spacing as a function of coupling power ratio for the modulator depicted in FIG. 1B in accordance with one embodiment;

[0025] FIGS. 6A and 6B are graphs showing the transfer functions of the modulator depicted in FIG. 1B in the through port and drop port, respectively, for several levels of lossy modulation in accordance with one embodiment;

[0026] FIG. 6C is a pole-zero plot illustrating lossy modulation of the modulator depicted in FIG. 1B in accordance with one embodiment;

[0027] FIG. 6D is a graph illustrating the power transmission in the through port of the modulator depicted in FIG. 1B as a function of the level of lossy modulation in accordance with one embodiment;

[0028] FIG. 7A is a drawing illustrating conceptually a second-order resonant modulator in accordance with various embodiments;

[0029] FIG. 7B is a drawing illustrating schematically an implementation of a second-order modulator including two microring resonators in accordance with one embodiment;

[0030] FIGS. 8A and 8B are pole-zero plots for the through and drop ports, respectively, of a second-order resonant modulator with two modulated resonators in accordance with one embodiment;

[0031] FIG. 9 is a graph showing the transfer functions of a second-order resonant modulator with two modulated resonators in the through port and drop port in accordance with one embodiment;

[0032] FIGS. 10A and 10B are pole-zero plots for the through and drop ports, respectively, of a second-order resonant modulator with a single modulated resonator in accordance with one embodiment;

[0033] FIGS. 11A and 11B are graphs showing the transfer functions of a second-order resonant modulator with two modulated resonators in the through port and drop port, respectively, for several modulation levels in accordance with one embodiment;

5 [0034] FIG. 12A is a drawing illustrating conceptually a third-order resonant modulator in accordance with various embodiments;

[0035] FIG. 12B is a drawing illustrating schematically an implementation of a third-order modulator including three microring resonators in accordance with one embodiment;

[0036] FIG. 13A is a drawing illustrating schematically a higher-order resonant modulator with a chain of microring resonators in accordance with one embodiment;

10 [0037] FIG. 13B is a drawing illustrating schematically a higher-order resonant modulator with a ring of microring resonators in accordance with one embodiment;

[0038] FIG. 14 is a drawing illustrating schematically a first-order modulator including a microring resonator and a Y waveguide junction in accordance with one embodiment;

15 [0039] FIGS. 15A-15B are drawings illustrating schematically symmetric and asymmetric modes in a Y waveguide junction in accordance with various embodiments;

[0040] FIGS. 15C-15D are drawings illustrating schematically symmetric and asymmetric modes in a multimode interference coupler in accordance with various embodiments;

[0041] FIG. 16A is a drawing illustrating schematically a first-order modulator including a figure-eight resonator and a directional coupler in accordance with one embodiment;

20 [0042] FIG. 16B is a drawing illustrating schematically a first-order modulator including a figure-eight resonator and a Y waveguide junction in accordance with one embodiment;

[0043] FIG. 17A-17B are drawings illustrating schematically second-order modulators with waveguide crossings in accordance with various embodiments;

25 [0044] FIG. 18 is a drawing illustrating schematically a second-order modulator with two mutually coupled microring resonators in accordance with one embodiment;

[0045] FIGS. 19A-19C are drawings illustrating schematically interchangeable coupling structures in accordance with various embodiments;

30 [0046] FIGS. 20A-20C are drawings illustrating schematically equivalent topologies of first-order modulators with a coupled-resonator pair and a directional coupler in accordance with various embodiments;

[0047] FIG. 21 is a drawing illustrating schematically a first-order modulator with a standing-wave cavity coupled to the waveguides via magnetooptic circulators in accordance with one embodiment;

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[0048] FIG. 22 is a drawing illustrating schematically a first-order modulator with a standing-wave cavity pair coupled to the waveguides via directional couplers in accordance with one embodiment; and

[0049] FIGS. 23A-23B are a perspective drawing and a cross-section, respectively, of a third-order resonant modulator wherein the active and passive resonators are in different layers in accordance with one embodiment.

DESCRIPTION

[0050] In general, the invention relates to optical intensity modulators. An optical modulator receives monochromatic light (typically, narrow-bandwidth laser light) at an input port, and provides intensity-modulated light at an output port. A variety of mechanisms may be employed to effect the intensity modulation. In resonant modulators, the laser light passes through a resonator structure whose resonance frequency and/or absorption properties are variable (i.e., an active resonator). For example, the electrooptic effect may be used to vary refractive index, and hence the resonance frequency, of the resonator structure, which passes the laser light only when the resonance frequency substantially coincides with the laser frequency (i.e., when the resonance band and the laser line overlap), and blocks the laser light when the resonance frequency is detuned from the laser frequency. The absorption properties may be modulated using electroabsorption based on, for example, the Franz-Keldysh or quantum-confined Stark effect. Carrier injection in silicon structures may be employed to change both the refractive and the absorptive properties (i.e., the complex index) of the resonator structure.

[0051] Modulators in accordance with various embodiments include two waveguides coupled via a resonant path as well as via a direct, broadband path, as further described below. The first waveguide contains an input port and a through port, and the second waveguide contains a drop port. Light that enters through the input port results in two complementary intensity-modulated signals in the drop and through ports. The transmission of an input signal from the input port to the two output ports (also referred to as the amplitude responses) may be characterized with two transfer functions, each providing the fraction of incoming power that is transmitted at the respective port as a function of frequency detuning from the resonance frequency. The transfer function properties depend on various parameters associated with the coupling paths, such as, e.g., the resonance frequency of the resonant path, coupling strengths, losses, and/or phase shifts.

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[0052] FIGS. 1A and 1B illustrate an exemplary single-resonance optical modulator device 100 in accordance with one embodiment. The modulator includes two waveguides 102, 104 coupled by an active optical resonator 106 such as, e.g., a microring resonator, and by a directional coupler 108 with coupling power ratio κ . One of the waveguides provides both the input port 110 and the through port 112 (labeled “output q”), and the other waveguide provides the drop port 114 (labeled “output q’”). The resonator 106 is characterized, absent modulation (i.e., in the “off” state), by a resonance frequency ω_0 and a resonator decay rate $r_{\text{total}} = r_i + r_o + r_l$, wherein r_i and r_o are the decay rates due to coupling to the waveguides 102 and 104, respectively, and r_l is the decay rate due to cavity losses (i.e., absorption of light in the resonator 106). The coupling rates r_i and r_o can be tuned by varying the distance between the resonator 106 and the waveguides 102, 104. Loss rate r_l and resonance frequency ω_0 are controllable through the selection of suitable materials and dimensions for the resonator. For example, the resonance frequency of a microring resonator is an inverse function of the ring radius. As illustrated, the modulator system 100 may also include phase shifters 116 (such as in one or both waveguides, which introduce a differential phase shift Φ between the through and drop ports 112, 114. Phase shifters may be implemented using, for example, waveguide sections where the phase shifts are effected through the thermo-optic effect—via the thermo-optic coefficient of the waveguide core and/or cladding material(s)—by providing local heating, which may be accomplished by placing microheaters in proximity; waveguide sections comprising a p-i-n junction where phase shifts are created by generating a carrier plasma in the optical guiding region, e.g., via carrier injection or depletion; waveguide sections comprising an electrooptic material, such as a polymer, and actuated by forming an electric field in the waveguide region by application of a voltage across integrated electrodes; and/or resonators tuned near the wavelength of operation of the modulator, similarly using thermo-optic, carrier plasma, or electrooptic effect applied to the resonant cavity. The parameters ω_0 , r_i , r_o , r_l , κ , and Φ can be chosen by design of the device 100 (within limits), and thus constitute six degrees of freedom that may be used to optimize the device.

[0053] The transfer functions of the modulator device 100, which is conceptually illustrated in FIG. 1A, are shown FIGS. 2A and 2B for the loss-less case ($r_l = 0$) for three values of the coupling power ratio κ . The power is split between the through and drop ports, whose corresponding transfer functions add up to 1 for all frequencies. (In the lossy case, i.e., for $r_l >$

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0, the sum of the transfer functions would be less than 1, and might vary with frequency.) For $\kappa = 0$, the transfer functions 200a, 200b show a zero 202 in the power transmission to the through port, and a pole (i.e., local maximum 204) in the power transmission to the drop port at the resonance frequency (which corresponds to zero frequency detuning $\delta\omega$). For $\kappa = 0.2$ and 0.5, the transfer functions of the through port and the drop port each include both a pole (near the maximum 206) and a transmission zero 208 or 209, respectively, at finite frequency detuning $\delta\omega$ from resonance. This, in turn, allows full modulation between approximately 100% and 0% of the input signal amplitude in each port. In a first modulation state ("off"), a monochromatic input signal is transmitted to the through port (by 100% for loss-less systems), corresponding to a transmission zero in the drop port at the signal frequency. In a second modulation state ("on"), the spectral response of the device is shifted so that, at the signal frequency, the through port has a transmission zero, and the signal is transferred to the drop port.

[0054] The effect of the design parameter values on the transfer function properties can be calculated using coupled-mode theory in time (CMT), and making the assumption that the photon lifetime in the resonator is much longer than the center frequency optical period and the round-trip time and that the system is reflection-less (which is the case for a microring resonator). The transmission amplitudes in the through and drop ports are:

$$T_{through} = \frac{1}{j\delta\omega_o + r_{total}} \left[\sqrt{1-\kappa} (j\delta\omega_o + r_l + r_o - r_i) e^{+j\phi/2} + j\sqrt{\kappa} \mu_i \mu_o e^{-j\phi/2} \right]$$

$$T_{drop} = \frac{1}{j\delta\omega_o + r_{total}} \left[-j\sqrt{\kappa} (j\delta\omega_o + r_l + r_o - r_i) e^{+j\phi/2} - \sqrt{1-\kappa} \mu_i \mu_o e^{-j\phi/2} \right]$$

where $\mu_i = \sqrt{2r_i}$ and $\mu_o = \sqrt{2r_o}$.

[0055] The wavelength-dependent behavior of device 100 is determined by the pole and zero positions in the complex frequency plane. The pole associated with the response maximum 206, which is the same for the through port and the drop port, resides at the complex resonant frequency ω_p formed of the resonant frequency ω_o and the total photon decay rate r_{total} :

$$\omega_p = \omega_o + jr_{total}$$

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The zeros 208 for the two response functions are, respectively:

$$\omega_{z, \text{through}} = \omega_0 + j(r_i + r_o - r_i) + 2\sqrt{\frac{Kr_i r_o}{1-K}} e^{-j\phi} e^{-j\pi}$$

$$\omega_{z, \text{drop}} = \omega_0 + j(r_i + r_o - r_i) + 2\sqrt{\frac{(1-K)r_i r_o}{K}} e^{-j\phi}$$

5 **[0056]** FIG. 3 illustrates the pole 206 and zero 208, 209 positions geometrically in the complex plane with origin at the resonance frequency ω_0 in the non-modulated (“off” state). Resonator loss r_i pushes the pole 206 and zeros 208, 209 collectively up along the imaginary axis, and the differential phase Φ rotates the zeros 208, 209 in the complex plane about the point $\omega = \omega_0 + j(r_i + r_o - r_i)$. In other words, the phase shift Φ corresponds to the orientation
10 angle in the complex-frequency plane of a line connecting the transmission zeros 208, 209 (i.e., the slope of the line is the trigonometric tangent of Φ). When the resonance frequency of the device is modulated, the transfer functions, and thus the pole associated with the maximum 206 and zeros 208, 209, translate left or right. Therefore, in order to achieve a sharp transition in the amplitude response for refractive-index (loss-less) modulation, the design parameters may
15 be selected such that both zeros fall on the real-frequency axis and the spacing between them is minimized.

[0057] To place both zeros on the real-frequency axis, the resonator loss and coupling rates may be chosen so that $r_i = r_o + r_i$, and the phase shift Φ set to zero (e.g., by not including phase shifters 116 in device 100). The transfer functions shown in FIGS. 2A-2B, for example, are
20 computed using $r_i = r_o = 0.5$, $r_i = 0$, and $\Phi = 0$. The properties of a device having both zeros real in frequency are illustrated in FIGS. 4A-4D. FIG. 4A indicates the positions of the poles and zeros, and their direction of motion during modulation of the resonance frequency of the active optical resonator 206. The transfer functions for the through port and drop port are shown in FIGS. 4A and 4B, respectively, for various levels of modulation m between the off-state ($m=0$),
25 corresponding to no modulation, and the on-state ($m=1$), corresponding to full modulation. The vertical shaded line indicates the input signal frequency. As can be seen, the input signal, which is placed at the position of the zero in the drop port, will see the full transmission in the drop port, corresponding to the zero in the through port, when the frequency shift due to modulation equals the spacing between the zeros. FIG. 4D shows the intensity in the through
30 port over the full range of modulation levels m .

[0058] To enable large modulation in the signal strength with small actuation, small distances between the transmission zeros are advantageous because they result in short transitions between a full 100% and a 0% transmission in each port. Minimizing the spacing between the zeros for a fixed photon lifetime provides the greatest modulation efficiency for a given modulation speed. The distance $\Delta\omega_z$ between the transmission zeros 208 is a function of the coupling power ratio κ : $\Delta\omega_z = 2\sqrt{r_{ir0}} \frac{1}{\sqrt{\kappa(1-\kappa)}} e^{-j\phi}$. As illustrated in FIG. 5, it may be minimized by choosing κ to fall in the range between approximately 5% and 95%, preferably between 13% and 87%, more preferably between 49% and 51%.

[0059] The modulator device 100 may also be used for small-signal modulation, i.e., intensity modulation of the output signal around a certain intensity value below 100% transmission by only a small fraction of that value. For small-signal modulation, only the slope of the transfer function at the selected intensity value matters, and is preferably maximized. This maximization occurs at $\kappa = 1/2$. Thus, in preferred small-signal modulation embodiments, κ is likewise chosen to fall in a range around 50% (e.g., between 5% and 95%, preferably between 13% and 87%, more preferably between 49% and 51%.)

[0060] Using loss-less modulation mechanisms, e.g., based on the linear electrooptic effect (which is used, e.g., in LiNbO₃) or the thermooptic effect (typically used in semiconductor- or polymer-core structure), the spectral response of the system (including the poles and transmission zeros depicted in FIG. 2) is shifted in frequency due to a change in the refractive index of the resonator. However, if lossy modulation, e.g., through carrier injection, is utilized, both the resonance frequency and the absorption of the resonator will change. As a result, in general, the poles and transmission zeros are shifted along both the real and imaginary axes. This situation is illustrated in FIGS. 6A-6D.

[0061] As shown in FIGS. 6A and 6B, modulation results in this case not only in a shift of the transfer functions, but also in a decrease in their maxima. The sum of signal intensities in the through and drop ports decreases with increased modulation level, the remainder of the input signal frequency being lost in the modulation process. Assuming that the resonator 106 is lossless in the off-state, a large-signal modulation swing from 100% to 0% in the through port may nonetheless be achieved by designing the modulator such that the transmission zero in the

drop port in the off-state lies on the real-frequency axis, and the phase shift Φ is equal to the modulation angle, whose tangent is the ratio of a change in resonator loss and a corresponding change in the resonance frequency due to modulation. In other words, with reference to FIG. 6C, the phase Φ is chosen such that modulation moves the zeros along the line that connects them in the complex frequency plane. Then, the through port has a transmission zero at real frequency in the shifted modulation state (“on”).

[0062] The off-state zero may be placed on the real-frequency axis by choosing $r_i > 0.5$ (corresponding to an over-coupled regime) and the coupling power ratio κ such that, for $\Phi \geq 0$ (i.e., blue-shifting lossy modulation),

$$\kappa = \frac{1}{1 + \frac{(1 - 2r_i)^2}{4r_i(1 - r_i - r_l)) \sin^2 \phi}}$$

and for $\Phi \leq 0$ (i.e., red-shifting lossy modulation),

$$\kappa = \frac{1}{1 + \frac{4r_i(1 - r_i - r_l) \sin^2 \phi}{(1 - 2r_i)^2}}.$$

The over-coupled regime compensates for the losses in the on-state, and brings the system back to the critical coupling condition.

[0063] The zero-spacing may be minimized, and thus the sensitivity of the modulator maximized, by selecting r_i to be

$$r_{i, opt} = \begin{cases} \frac{1}{2} + \frac{|\sin(2\phi)|}{4 \cos^2 \phi}, & |\phi| \leq \frac{\pi}{4} \text{ or } \frac{3\pi}{4} \leq |\phi| \leq \pi \\ 1, & \end{cases}$$

with corresponding coupler ratios κ

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$$\kappa_{opt} = \begin{cases} 1 - \frac{1}{2} \sec^2 \phi, & 0 \leq \phi \leq \frac{\pi}{4}, \frac{3\pi}{4} \leq \phi \leq \pi \\ 0, & \frac{\pi}{4} \leq \phi \leq \frac{3\pi}{4} \\ \frac{1}{2} \sec^2 \phi, & -\pi \leq \phi \leq -\frac{3\pi}{4}, -\frac{\pi}{4} \leq \phi \leq 0 \\ 1, & -\frac{3\pi}{4} \leq \phi \leq -\frac{\pi}{4} \end{cases}$$

[0064] The device depicted in FIG. 1B may be modified in various ways. For example, as illustrated in FIG. 7B for a modulator device 700, the broadband directional coupler may be replaced by a second resonant coupler 702. Such an optical modulator device constitutes a second-order resonant system with two poles and two zeros in the through port, and two poles and one zero in the drop port, as shown in FIG. 7A. It may be designed to avoid excessive losses in the through port at off-resonance wavelengths, and may thus be advantageously employed in wavelength-division multiplexed systems, as further explained below.

[0065] The transfer properties of device 700 depend on the resonance frequencies and coupling and loss decay rates of both resonator 106 (w_0, r_i, r_o, r_l) and the second resonator 702 (w_0', r_i', r_o', r_l'), as well as the phase shift Φ . The transmission amplitudes in the through and drop ports are given by:

$$T_{through} = T_0 \left[(j\delta\omega + r_o + r_l - r_i)(j\delta\omega' + r_o' + r_l' - r_i')e^{-j\phi/2} + 4\sqrt{r_i r_o r_i' r_o'}e^{+j\phi/2} \right]$$

$$T_{drop} = T_0 \left[(j\delta\omega + r_o + r_l + r_i)2\sqrt{r_i' r_o'}e^{-j\phi/2} + (j\delta\omega' + r_o' + r_l' + r_i')2\sqrt{r_i r_o}e^{+j\phi/2} \right]$$

$$T_0 \equiv \frac{1}{(j\delta\omega + r_{total})(j\delta\omega' - r_{total}')$$

Assuming lossless resonators ($r = r_l' = 0$) and a lossless, fully refractive modulation of both resonators, the device 700 may be optimized by placing one zero from each port on the real frequency axis, as shown, for example, in FIGS. 8A (through port) and 8B (drop port). In one embodiment, this is accomplished by choosing $r_i = 0.25$, $r_o = 0.75$, $\Phi = 0.55\pi$, $w_0 = w_0'$, $r_i' = 0.2929$, and $r_o' = 1.7071$. The transfer functions for this choice of parameter values are shown in FIG. 9. The device has closely spaced transmission zeros in the through and drop port, which allows for efficient modulation. Moreover, the through port has full transmission far off

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resonance. Thus, the modulator may be placed onto a wavelength-division multiplexer bus, and modulate one of a comb of wavelengths, while not affecting the remaining wavelengths on the bus.

[0066] In some embodiments, only one of the resonators of device 700 (e.g., resonator 106) is modulated, while the other resonator (e.g., resonator 702) is passive. This increases energy-efficiency and reduces system complexity. In this case, the poles and zeros are translated together in the complex plane during modulation. The pole of the modulated resonator will be shifted, while the pole of the unmodulated resonator will stay fixed. The zeros may shift, in one embodiment, as illustrated in the pole-zero plots of FIGS. 10A and 10B. Therein, $r_i = r_o = 0.5$, and $\Phi = \pi/2$. Further, the coupling strengths r_i' and r_o' of the passive ring are chosen such that they effect a 3dB power drop at resonance. Preferably, but not necessarily, the line widths of the two resonator rings are equal, and, in that case, input and output coupling are related by $r_i' = \sin^2(\pi/8) = 0.146$, $r_o' = \cos^2(\pi/8) = 0.853$. The transfer functions of the through and drop ports for this embodiment are shown in FIGS. 11A and 11B, respectively.

[0067] In general, optical modulators in accordance with various embodiments of the invention may include N resonators and may, consequently, have N poles and up to N transmission zeros near a signal wavelength in each port. Typically, the number of poles N_p in each transfer function is equal to the number of resonant modes N (near the signal wavelength of interest). The number of transmission zeros at finite frequency detuning from resonance (N_{zt} , N_{zd} for the through and drop port responses, respectively) may differ between the two transfer functions. In general, it is equal to the number of poles, minus the smallest number of resonators that need to be traversed by light propagating from the input port to the respective output port (except that both the number of poles and the number of zeros for a transfer function may be reduced by the same number if one or more pole-zero cancellations occur, i.e., if a transmission zero occurs at the same location in the complex frequency plane as a system pole). The remaining $N_p - N_z$ zeros are typically at infinite frequency detuning or, in practice, at very large detuning (i.e., detuning much larger than the resonant system bandwidth).

[0068] Multiple resonators may be utilized in optical modulators to achieve high wavelength selectivity. Such systems provide multiple paths for light to travel from the input port to the through port. For example, in the second-order system depicted in FIGS. 7A and 7B

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and described above, the signal may travel directly from the input port to the through port through the first waveguide, or, alternatively, may traverse the structure comprised of the first resonator, the second waveguide, and the second resonator. Similarly, in a third-order resonator system, such as the one depicted in FIGS. 12A and 12B, the signal may travel, on its way from the input to the through port, through the first waveguide or through three microring resonators. In general, wavelength-selective resonant modulators described herein have two interferometric paths, one of which crosses a resonator (i.e., does not have a direct connection between the input and output ports). Off-resonant wavelengths see only one path (the direct path), and are not disturbed. Multiple-resonator modulators as described above have fewer transmission zeros at finite frequency detuning in the drop port than poles, as at least one transmission zero is at infinite frequency detuning. This results in a fast roll-off of the signal in the drop port near resonance and, consequently, in a signal quickly approaching 100% in the through port off resonance. As a result, multiple modulators at different wavelengths may be cascaded.

[0069] In some embodiments, the second-order structure depicted in FIG. 7B is generalized to higher order. For example, the modulator 1200 illustrated in FIG. 12B works as follows: the left and right microring resonators 106, 702, when in phase, couple coherently to the middle (bottom) microring resonator 1202, and transfer power at resonance to the drop waveguide 104, thus leaving little or no light in the through port. When the left microring 106 is modulated (i.e., shifted in resonance frequency), the relative phases change so that the left and right microrings 106, 702 excite the middle microring 1202 out of phase, so that no power builds up in the middle ring 1202, and all power continues to the through port. One advantage of such a device is that it still has only one cavity modulated to produce amplitude modulation, which renders it energy-efficient and simple to control and drive, but now the roll-off of the optical frequency response with increasing distance from resonance is of second order. This means that the response approaches 100% in the through port faster, so modulators can be cascaded at closer wavelength spacing without crosstalk. One approach to extend this to even higher order involves adding further resonators below the middle resonator 1202, between that resonator and the second waveguide 104. For example, as illustrated in FIG. 13A for a higher-order device 1300, the middle resonator 1202 may be coupled to the second waveguide 104 via a straight line of microring resonators 1302. This is sufficient to preserve interferometric cancellation in the through port (allowing a through-port zero and a drop-port zero near resonance), and multiple zeros at infinite detuning in the drop port. In an alternative higher-order modulator

device 1350, depicted in FIG. 13B, the input and drop waveguides 102, 104, are coupled via a ring of four microring resonators 1352, with each waveguide coupling directly to one of the microrings.

[0070] Various additional embodiments are illustrated in FIGS. 14-23. FIG. 14 illustrates a device 1400 otherwise similar to the device 100 depicted in FIG. 1B, wherein the directional coupler 108 is substituted by a Y-junction 1402, which combines the two waveguides 102, 104 to form a single output port. In this embodiment, the phase shift Φ may be adjusted by 90° . Power that would otherwise go to the drop port contributes to radiated losses; however, this is not a concern in many applications. FIGS. 15A-15D show how a symmetric mode is captured in the single-mode output waveguide, while an antisymmetric mode is radiated from the Y junction combiner (FIGS. 15A-15B) or equivalent multimode interference coupler (FIGS. 15C-15D).

[0071] A symmetric implementation is shown in FIGS. 16A, which utilizes a figure-eight resonator 1600 in place of the microring 106. This embodiment may also be used with a Y-junction 1402. The figure-eight resonator 1600 may include a low-loss crossing as described, for example, in U.S. Patent Application No. 12/288,716, filed on October 22, 2008, the entire disclosure of which is hereby incorporated herein by reference.

[0072] FIGS. 17A-17B illustrate alternative geometries for devices functionally equivalent to the second-order modulator 700 depicted in FIG. 7B. The alternative geometries may use waveguide crossings to make all ports accessible outside the device, and at the same time balance crossing-induced losses by symmetry. FIG. 18 illustrates yet another geometry that has two poles and one zero in the drop port, and is functionally similar to that of the device 700 depicted in FIG. 7.

[0073] FIGS. 19A-19C illustrates three coupling structures – a microring resonator 1900, a standing-wave cavity pair 1902, and a photonic-crystal cavity pair 1904 – any of which may be used to couple the waveguides 102, 104 (in place of, e.g., microring 106). If the two standing-wave cavities or photonic-crystal cavities are appropriately mutually coupled relative to their coupling to the waveguides, with appropriate phase shifts, then these three geometries are functionally similar, and may be used interchangeably. FIGS. 20A-20C show equivalent topologies to that of the device 100 depicted in FIG. 1B, which utilize a standing-wave cavity pair 1902 followed by couplers 2000, followed and preceded by couplers 2000, or preceded by couplers 2000, respectively. The cavities couple the two waveguides, and further couple to each other. Instead of standing-wave cavities, ring resonators or photonic crystal cavities may

be used. FIG. 21 illustrates yet another way of achieving a similar function as the ring device 100 depicted in FIG. 1B, using a standing-wave cavity 2100. This device further requires magnetooptic circulators 2102. In FIG. 22, a pair of standing-wave cavities 2200, excited through 3dB couplers 2202, is shown. In this case, the two cavities are identical and not coupled to each other.

[0074] As illustrated in FIGS. 23A-23B, the structure 1200 depicted in FIG. 12 may be realized with the active resonator 106 on a second material layer level, in order to allow the active ring 106 to have a ridge-waveguide design all around the ring.

[0075] Optical modulators in accordance with the present invention may be fabricated from various semiconductor and/or insulating materials, using standard lithography and etching techniques. The fabrication of silicon structures typically starts with a silicon-on-insulator (SOI) wafer, whose top silicon layer has a thickness suitable for single-mode strongly confined waveguides. To prepare the wafer for patterning, a resist layer may be spin-coated or otherwise placed on top of the silicon layer. For subsequent patterning by electron beam lithography, sesquisiloxane may be used for the resist. Alternatively, for optical lithography, a photoresist such as polymethyl methacrylate (PMMA) may be used. HBr-chemistry-based reactive-ion etching (RIE) may then be employed to etch the mask pattern into the silicon layer. After the resist has been removed, the patterned silicon structures (e.g., waveguides, resonators, etc.) appear as raised structures on the silica layer underneath. For photonics applications, the silica layer is preferably about 2-3 μm thick, which serves to avoid optical loss by leakage into the silicon substrate.

[0076] To facilitate optical modulation, active structures may be created by doping certain regions (e.g., a resonator ring intended to have variable absorptive and resonance properties). Regions not to be doped may be protected by one or more additional masks, formed, for example, of silicon nitride, and patterned by lithography and etching. Doping may be achieved by ion implantation through a mask, or by thermal diffusion in gas atmosphere containing the ion(s) of interest. Boron may be used for p-type doping, and arsenic or phosphorus may be used for n-type doping. Typical dopant concentrations are between 10^{16} and 10^{20} ions per cubic centimeter, depending on the p-i-n junction design. Alternatively, active structures may be created by lithographically patterning a layer of metal deposited above the waveguides into a microheater—a resistive metal part in proximity to the optical structure, but sufficiently displaced to avoid introducing substantial optical losses. Passing a current through the metallic microheater will generate heat and a temperature increase in a localized region, thus creating an

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index change and concomitant phase shift in the optical waveguides included in the local region. An alternative is to form microheaters by using doped silicon structures in the waveguide layer, or another material layer, for conduction. Another way to create active structures includes using an electro-optic material for the waveguiding structures, and
5 implementing electrodes that allow application of a voltage across the region containing the electro-optic waveguiding structures.

[0077] Similar techniques may be employed to fabricate non-silicon structures, such as structures based on III-V semiconductors like indium phosphide (InP), or on silicon nitride or other amorphous materials. Fabrication may again start with a substrate wafer, on top of which
10 an undercladding layer with a low index of refraction, and a semiconductor layer or high-index dielectric for the waveguide core are disposed in the order listed. The waveguides are then similarly formed by lithography and etching steps. In the cases of non-crystalline core materials, such as silicon nitride, the waveguide core (SiN) layer may be deposited by plasma-enhanced chemical vapor deposition (PE-CVD), a low-pressure chemical vapor deposition (LP-
15 CVD), or a vertical thermal reactor (VTR) process.

[0078] Having described certain embodiments of the invention, it will be apparent to those of ordinary skill in the art that other embodiments incorporating the concepts disclosed herein may be used without departing from the spirit and scope of the invention. Accordingly, the described embodiments are to be considered in all respects as only illustrative and not
20 restrictive.

[0079] What is claimed is:

CLAIMS

- 1 1. An optical modulator, comprising:
2 a first optical waveguide comprising an input port and a through port, the input port for
3 receiving an input signal;
4 a first optical resonator optically coupled to the first optical waveguide;
5 a second optical waveguide optically coupled to the first optical resonator and
6 comprising a drop port; and
7 a coupling structure optically coupling the first optical waveguide to the second optical
8 waveguide.
- 1 2. The optical modulator of claim 1 wherein the first optical resonator is optically active.
- 1 3. The optical modulator of claim 1 wherein the first optical resonator comprises at least
2 one of a microring resonator, a figure-eight resonator, a standing-wave cavity pair, or a
3 photonic crystal cavity pair.
- 1 4. The optical modulator of claim 1 wherein the coupling structure comprises a directional
2 coupler.
- 1 5. The optical modulator of claim 4 wherein the directional coupler couples between 13%
2 and 87% of the input signal from the first optical waveguide to the second optical waveguide.
- 1 6. The optical modulator of claim 1 wherein the coupling structure comprises one of a
2 waveguide junction or a multimode interference coupler joining the first and second
3 waveguides.
- 1 7. The optical modulator of claim 1 wherein the coupling structure comprises a second
2 optical resonator.
- 1 8. The optical modulator of claim 7 wherein the coupling structure further comprises the
2 first optical resonator.
- 1 9. The optical modulator of claim 7 wherein the first and second optical resonators are
2 coupled directly to the first optical waveguide and via at least a third optical resonator to the
3 second optical waveguide.

10. The optical modulator of claim 1 wherein the first optical resonator is located in a first layer of the optical modulator, and the first and second waveguides and coupling structure are located in a second layer of the optical modulator.

11. The optical modulator of claim 1 further comprising at least one phase shifter in at least one of the first and second waveguides between the first optical resonator and the coupling structure, the at least one phase shifter inducing a differential phase shift between the first and second waveguides.

12. The optical modulator of claim 11 wherein modulation from a first modulation state to a second modulation state is associated with a frequency detuning and an absorption detuning, and the differential phase shift is substantially equal to the inverse tangent of a ratio of the absorption detuning to the frequency detuning.

13. The optical modulator of claim 1 wherein (i) a transfer function from the input port to the through port comprises a transmission zero at a frequency of the input signal in a first modulation state, and (ii) a transfer function from the input port to the drop port comprises a transmission zero at the frequency of the input signal in a second modulation state.

14. An optical modulator, comprising:
an optical input port for receiving an input signal;
an optical through port;
an optical drop port; and
an optical resonator structure coupling the input port to the through port and the drop port,

wherein a transfer function from the input port to the through port comprises a transmission zero at a frequency of the input signal in a first modulation state, and a transfer function from the input port to the drop port comprises a transmission zero at the signal frequency in a second modulation state.

15. The optical modulator of claim 14 wherein the optical resonator structure comprises a plurality of optical resonators.

16. The optical modulator of claim 14 wherein modulation from the first modulation state to the second modulation state is associated with a frequency detuning and an absorption detuning, and a differential phase shift between the through and drop ports is substantially equal to the inverse tangent of a ratio of the absorption detuning to the frequency detuning.

- 1 17. A wavelength-selective optical modulator, comprising:
2 an optical input port;
3 an optical output port;
4 a first path connecting the optical input port to the optical output port, the first path
5 comprising at least two optical resonators; and
6 a second path connecting the optical input port to the optical output port via a structure
7 outside of the first path.
- 1 18. The wavelength-selective optical modulator of claim 17 wherein at least one of the
2 optical resonators is modulated, and at least one of the optical resonators is passive.
- 1 19. The wavelength-selective optical modulator of claim 17 wherein a transfer function
2 from the input port to the output port comprises a first transmission zero at a complex-
3 frequency detuning from a resonance of less than three 3dB bandwidths and a second
4 transmission zero at a complex-frequency detuning from the resonance of more than six 3dB
5 bandwidths.

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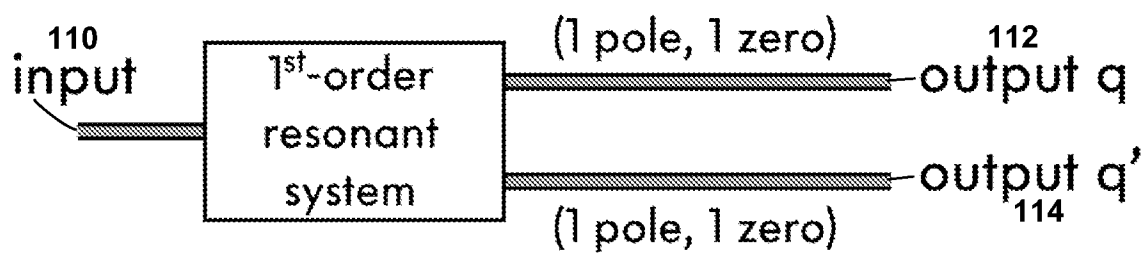


FIG. 1A

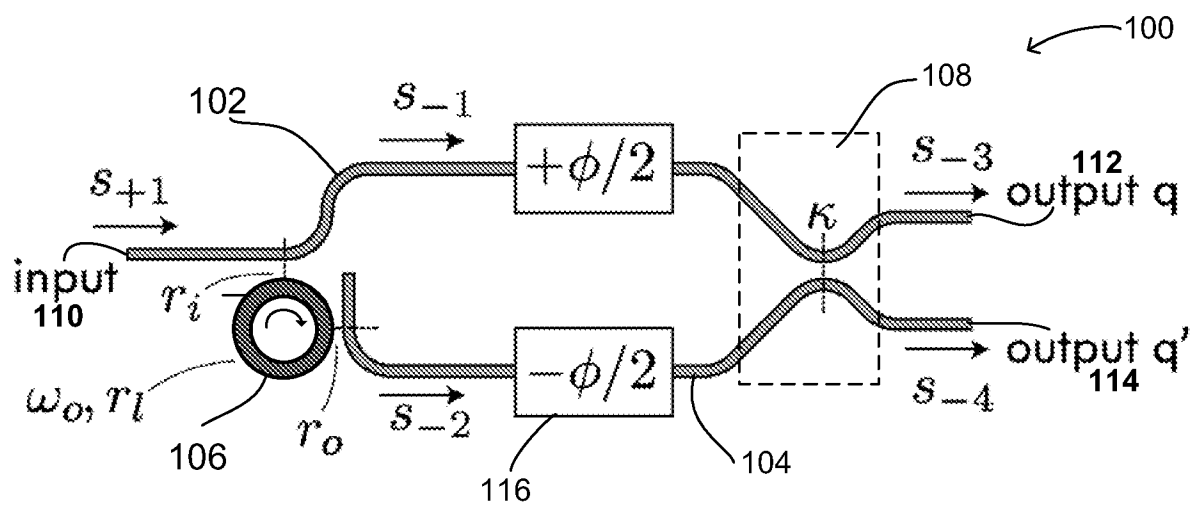


FIG. 1B

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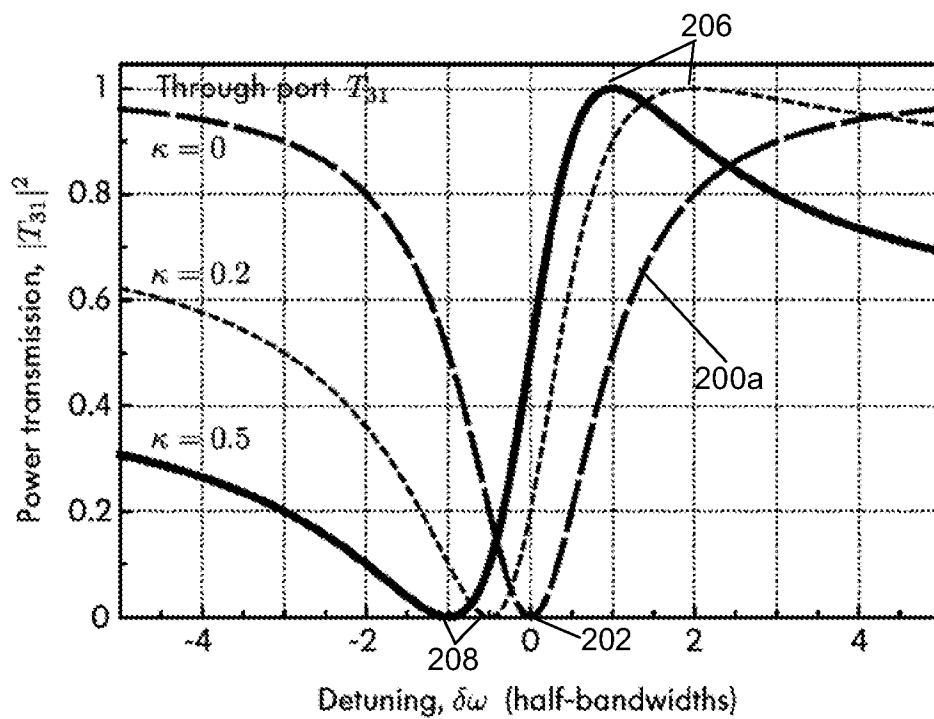


FIG. 2A

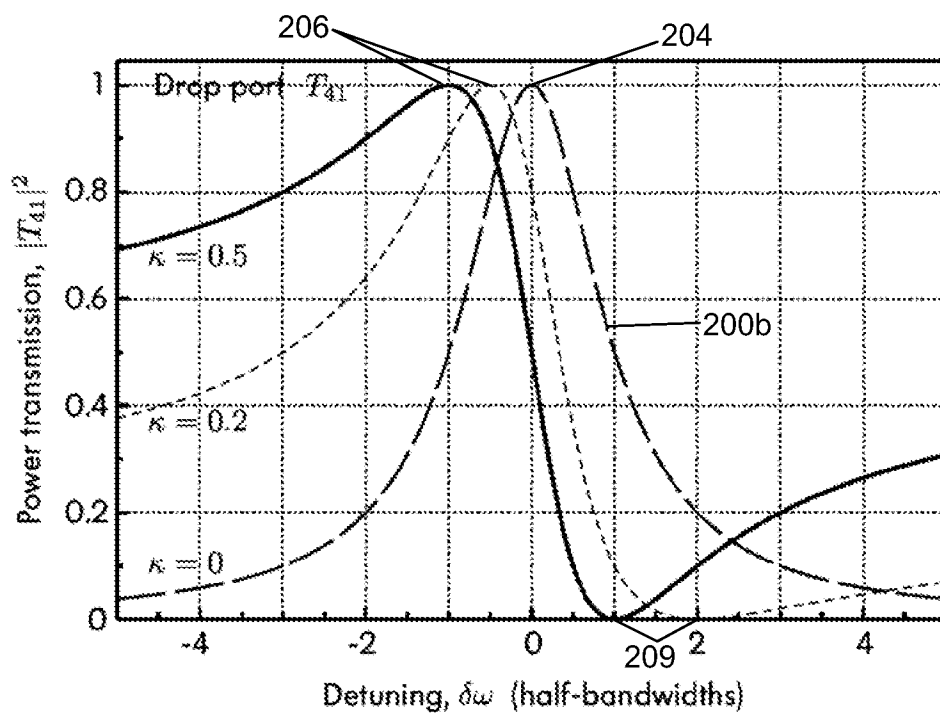


FIG. 2B

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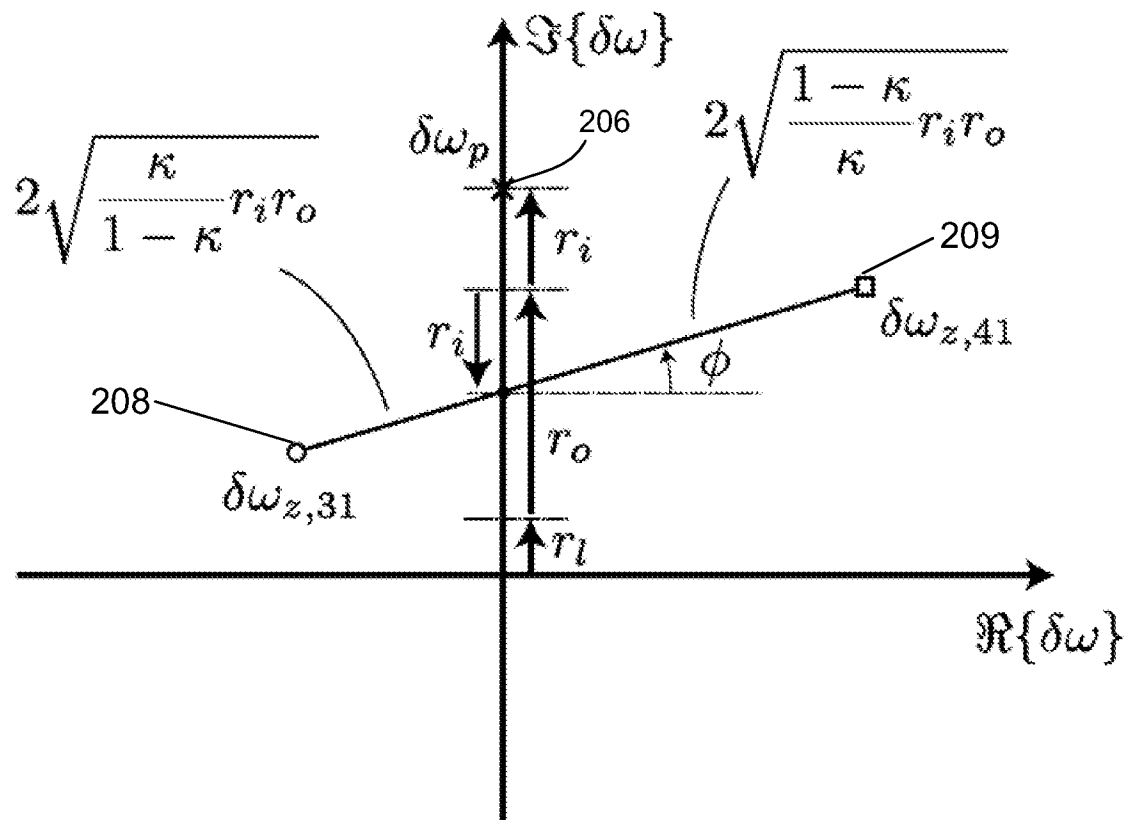


FIG. 3

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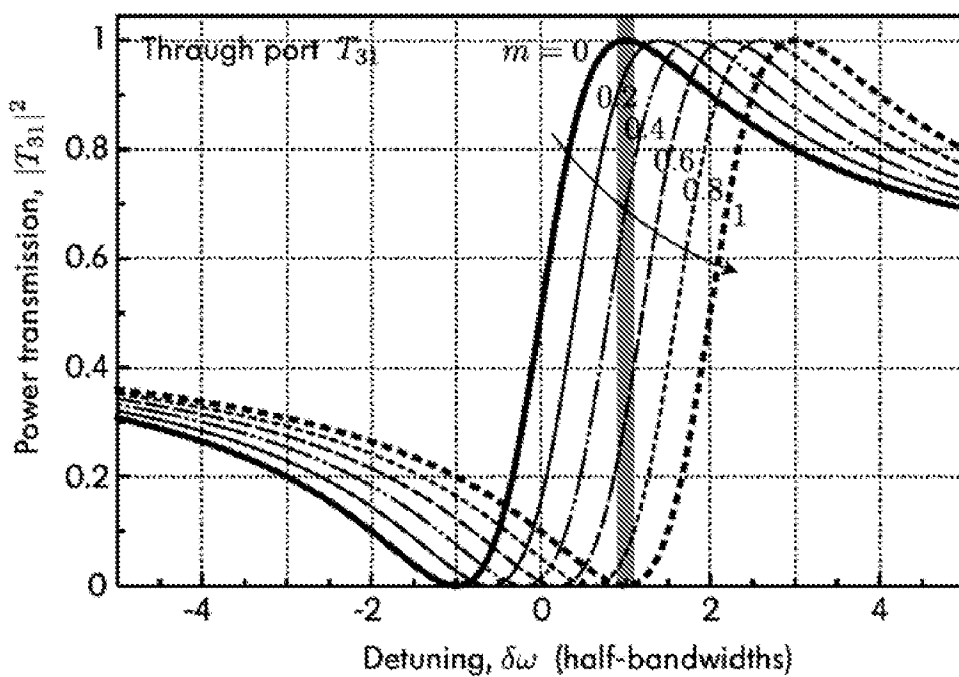


FIG. 4A

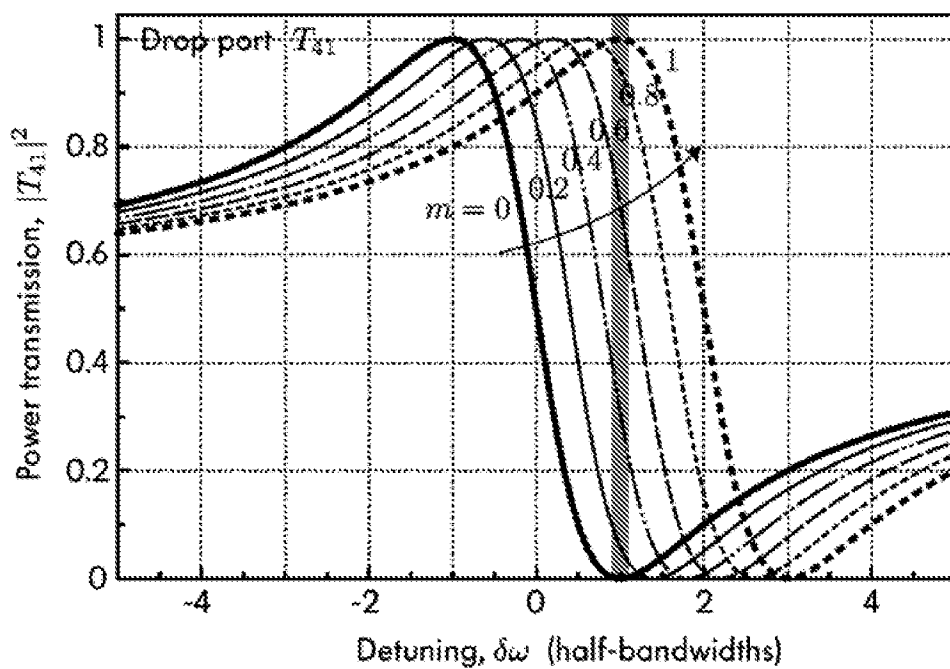
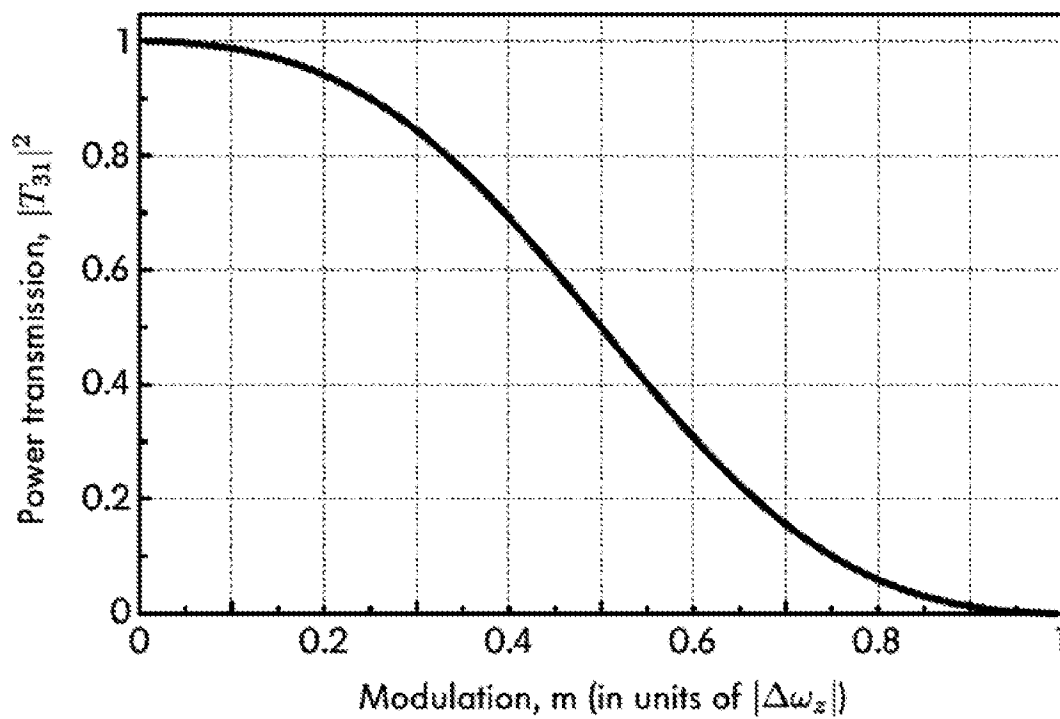
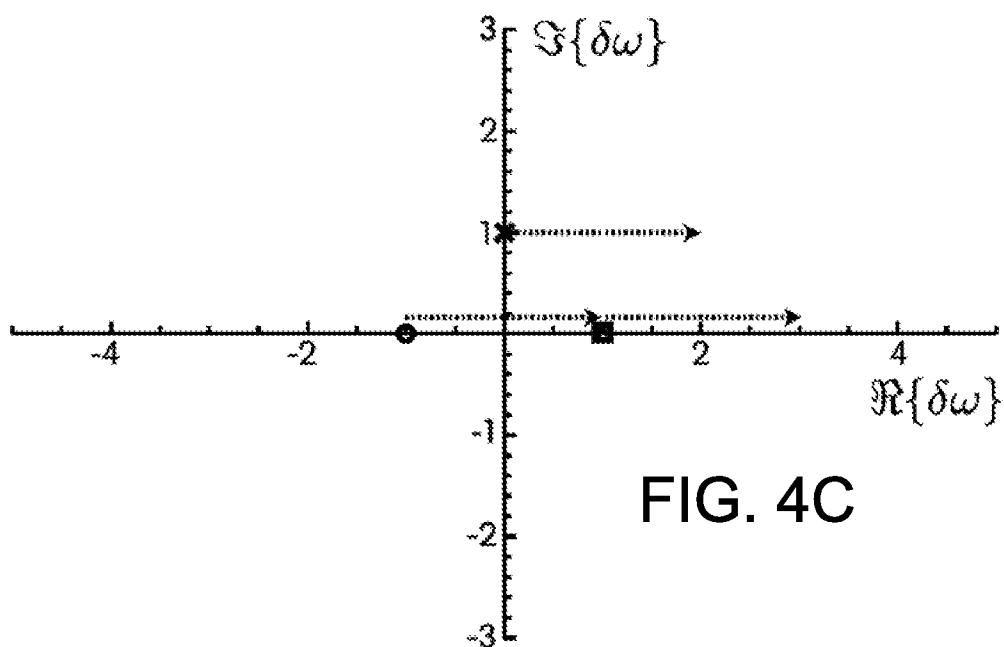


FIG. 4B

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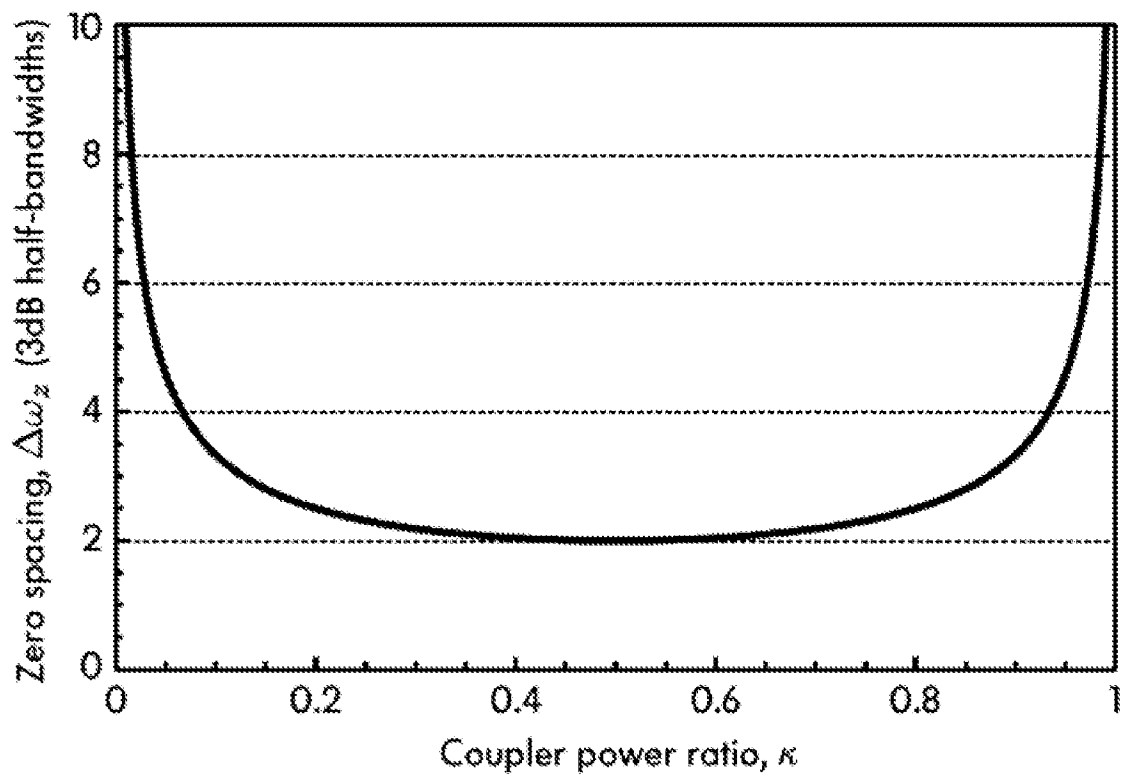


FIG. 5

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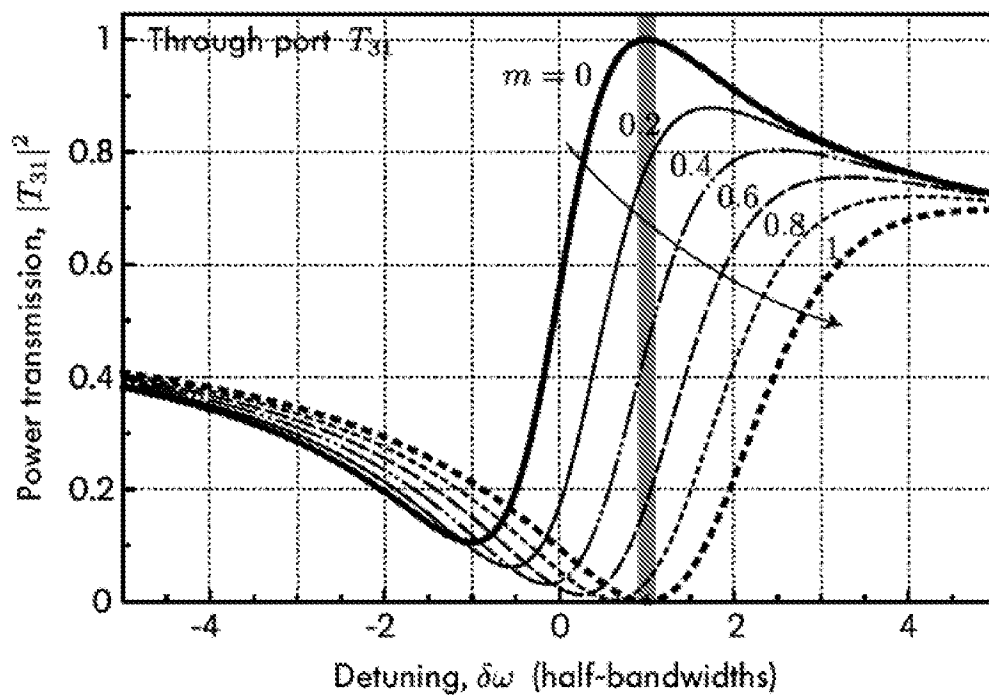


FIG. 6A

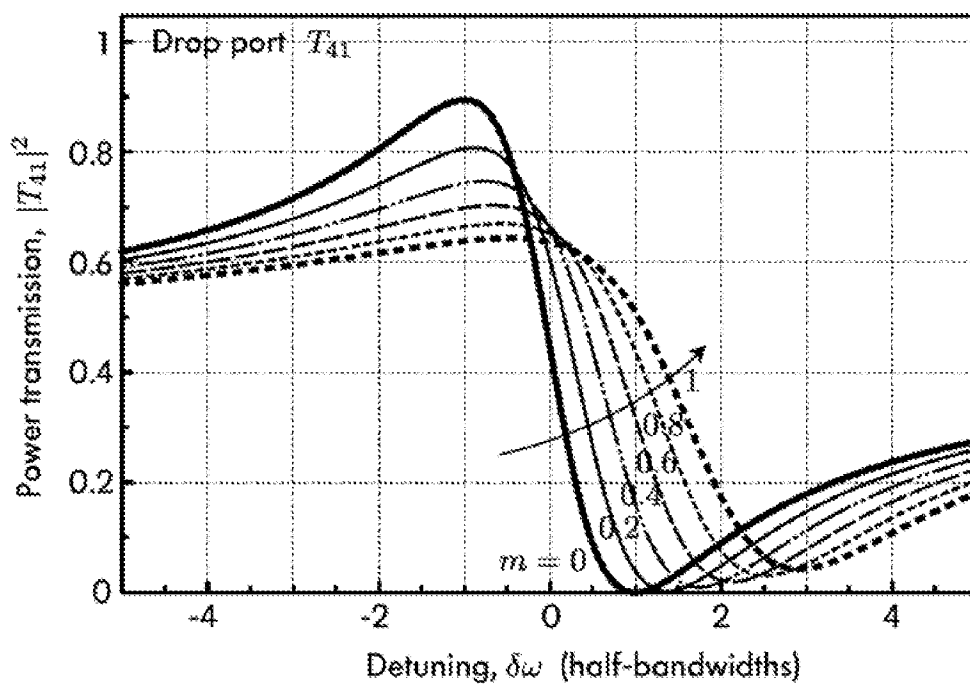
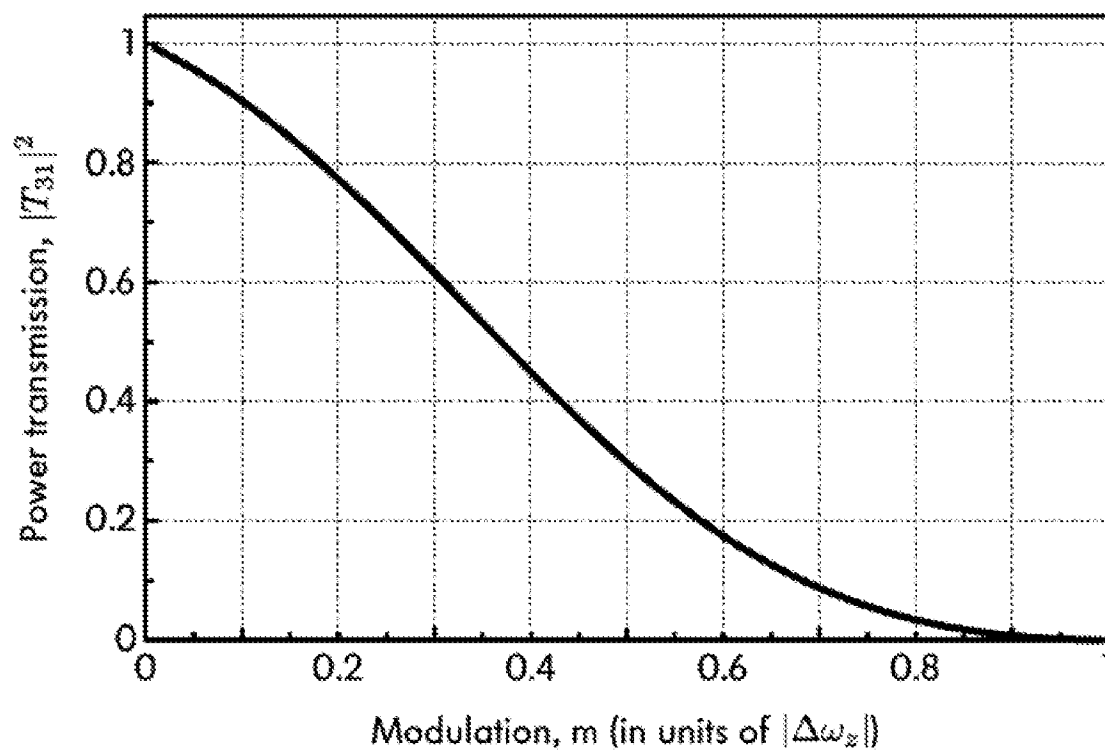
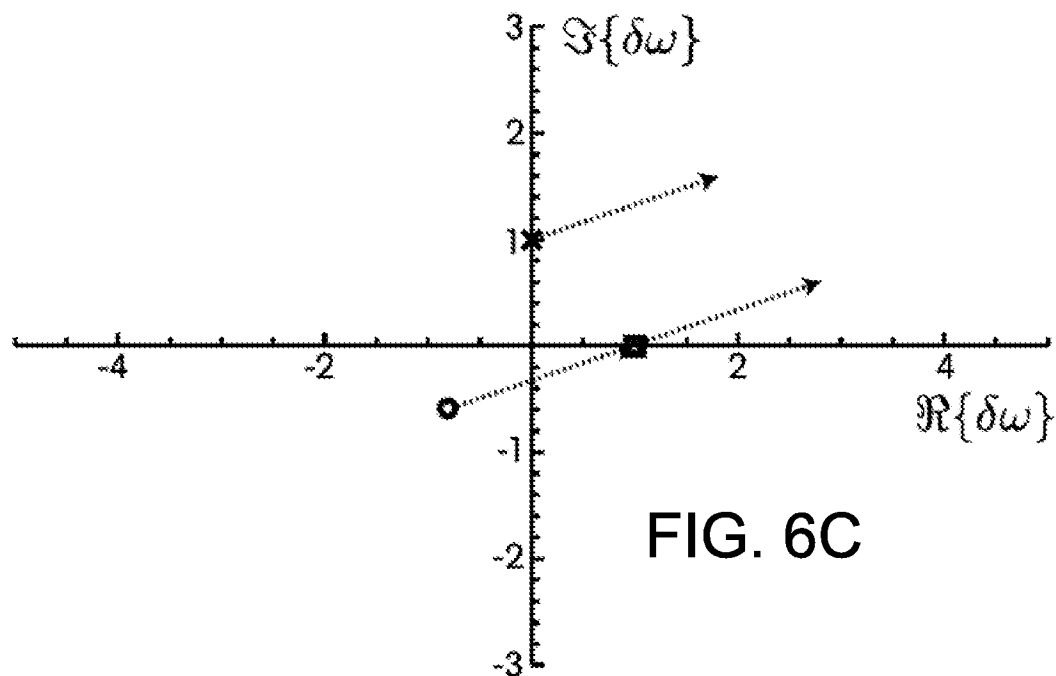


FIG. 6B

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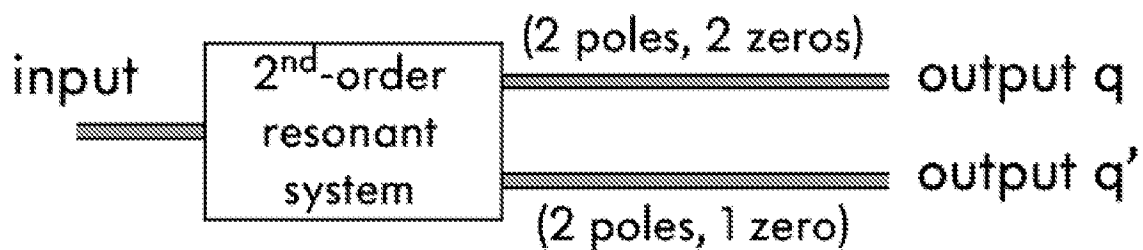


FIG. 7A

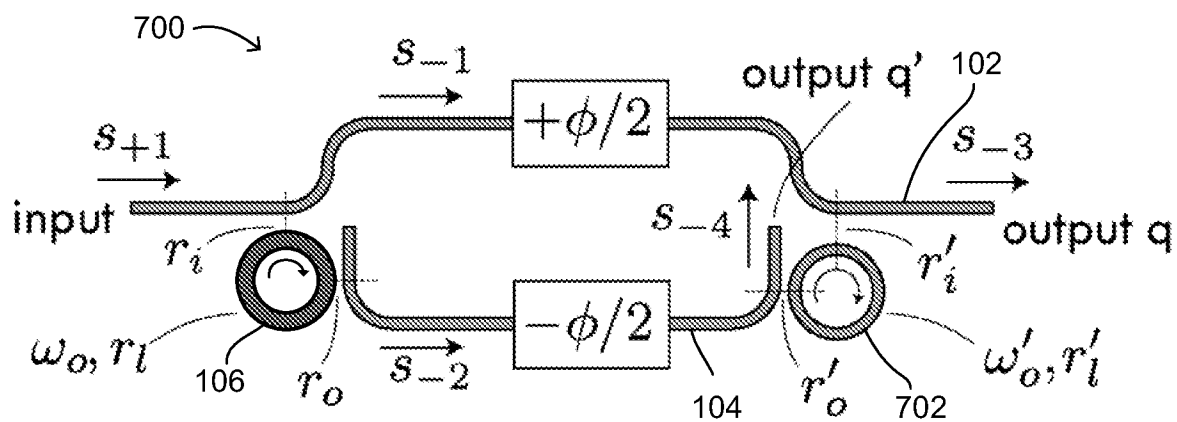
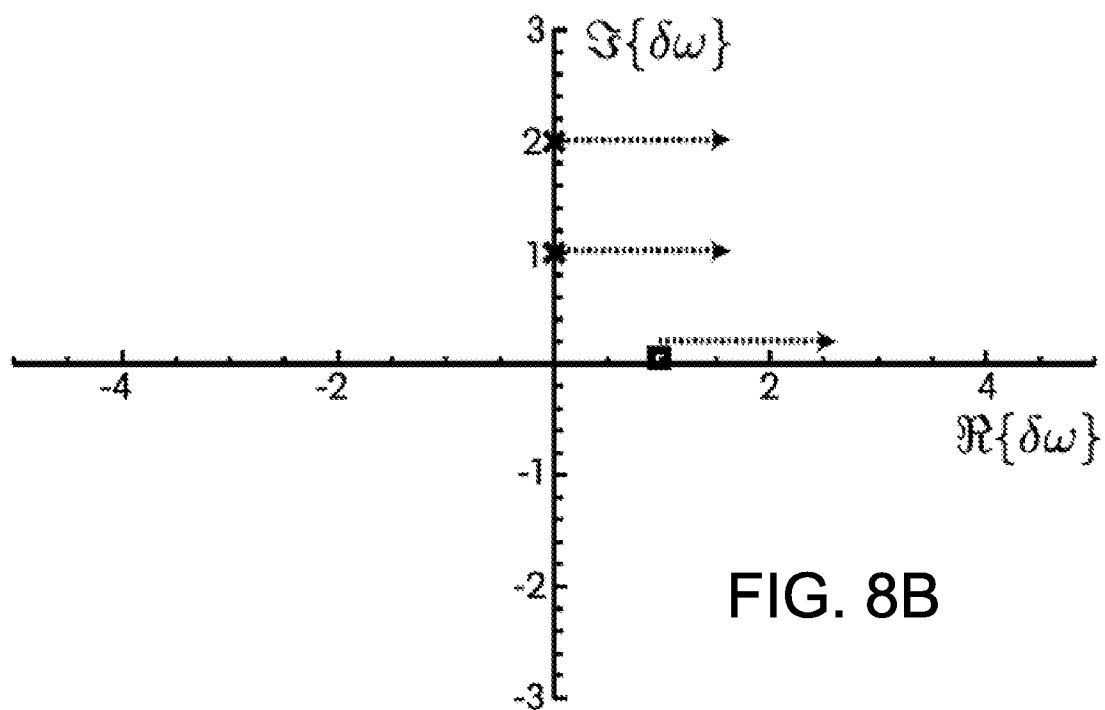
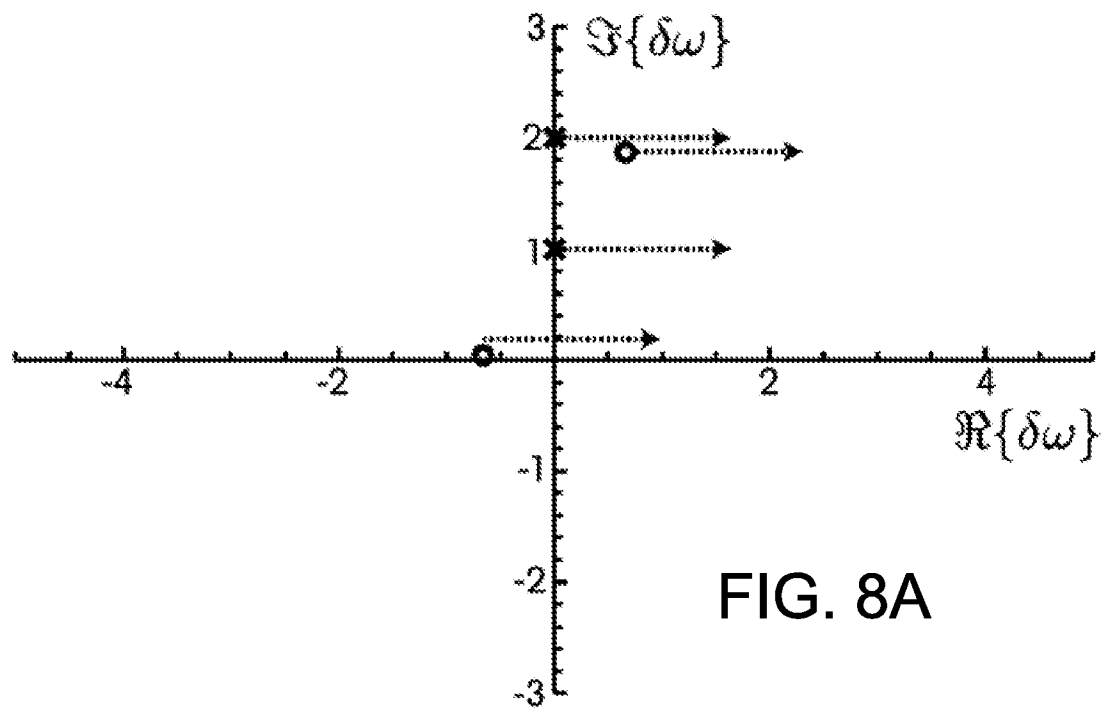


FIG. 7B

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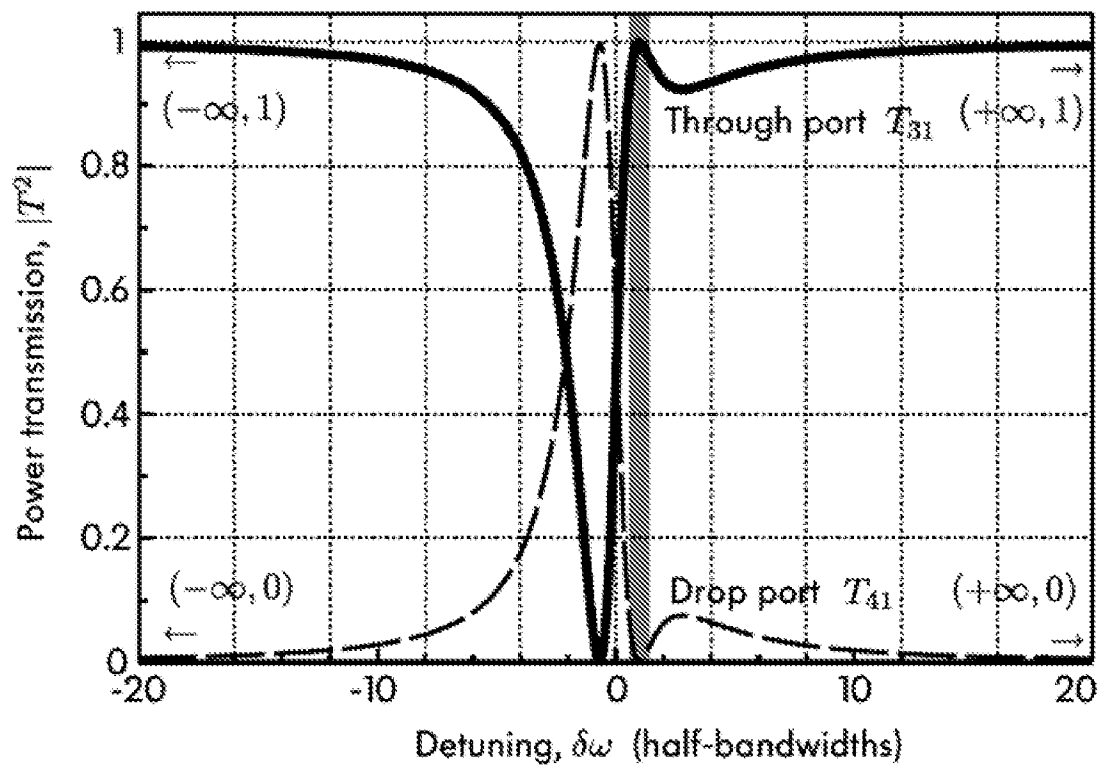
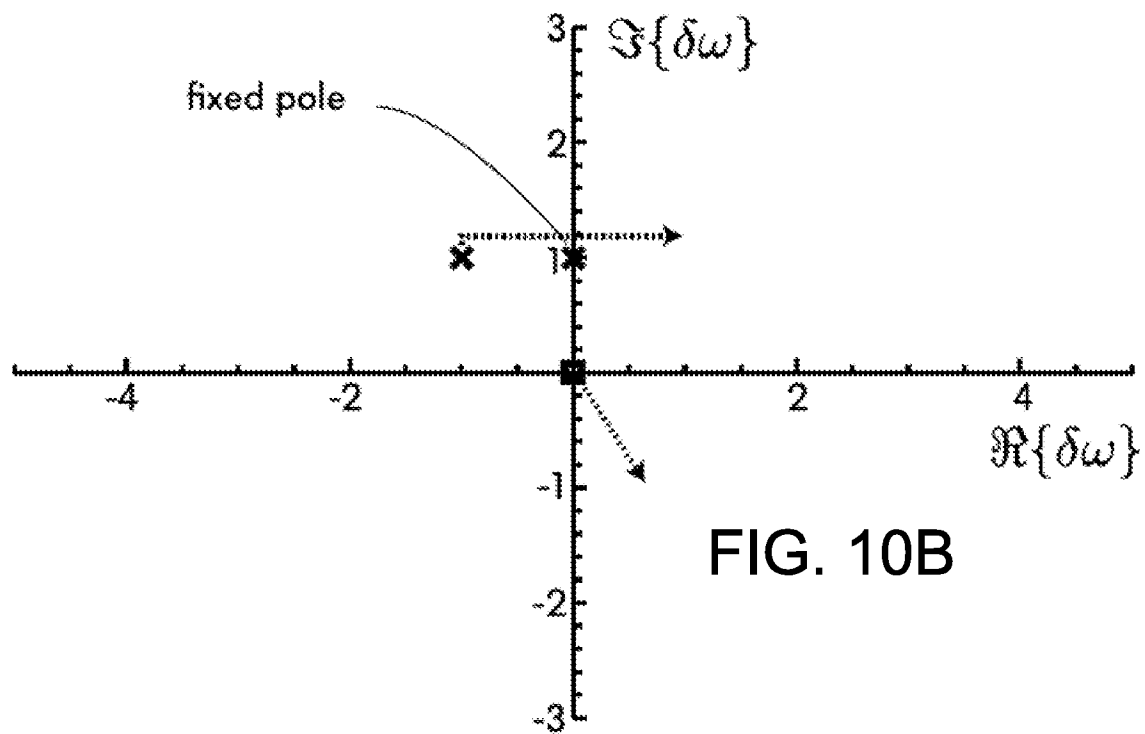
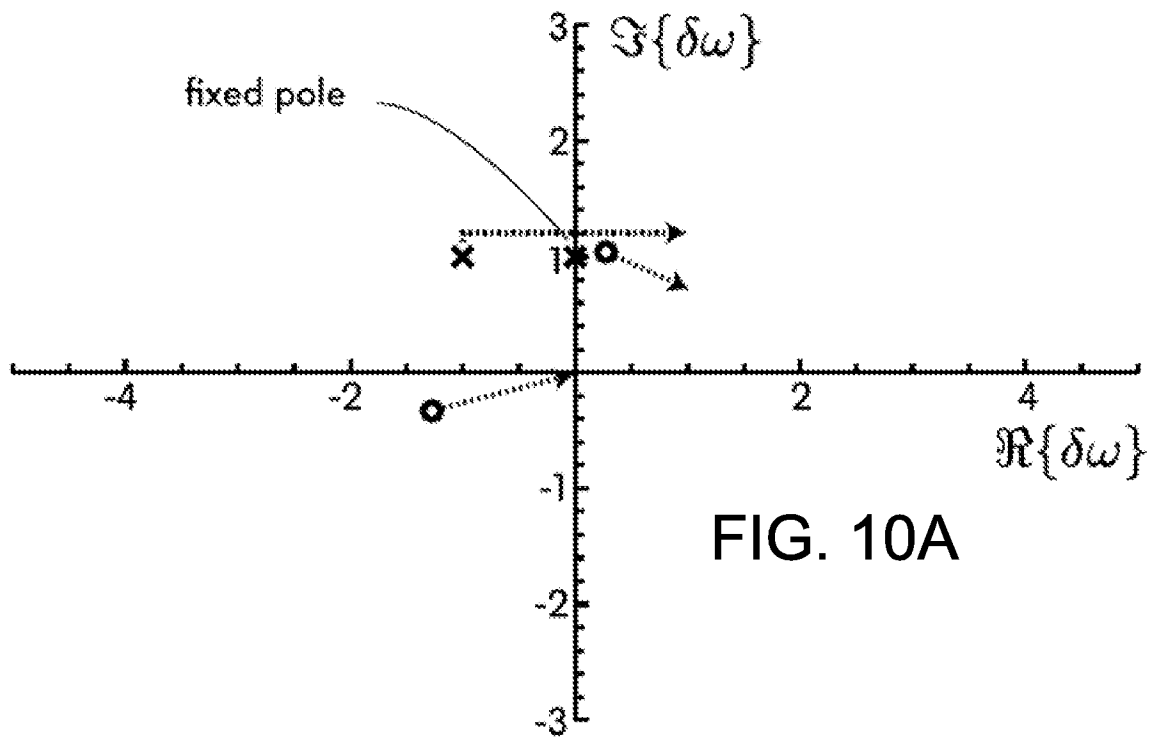


FIG. 9

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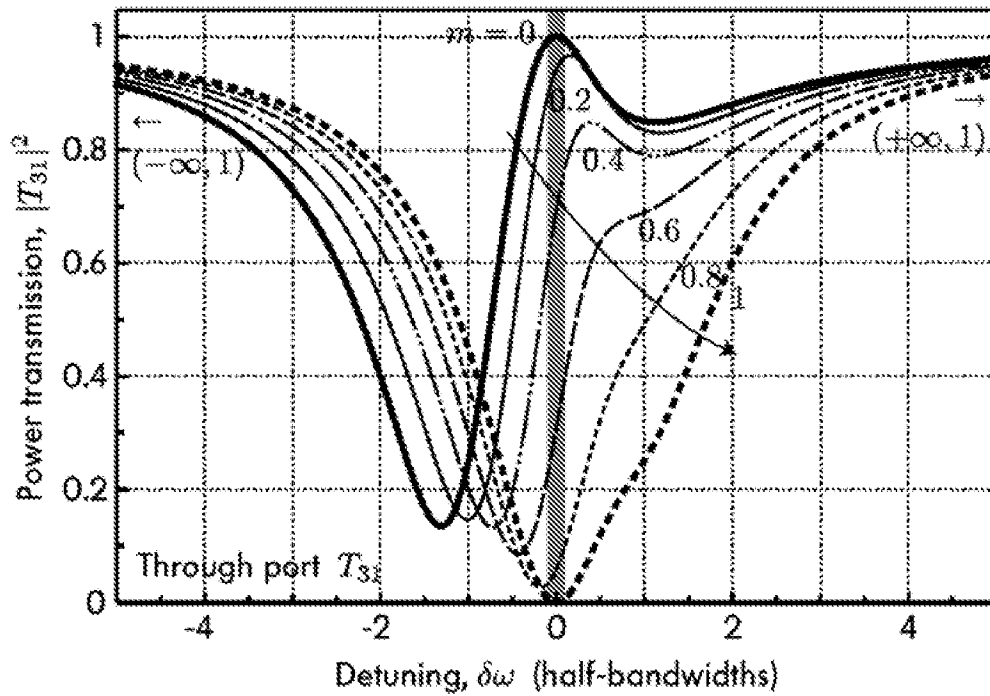


FIG. 11A

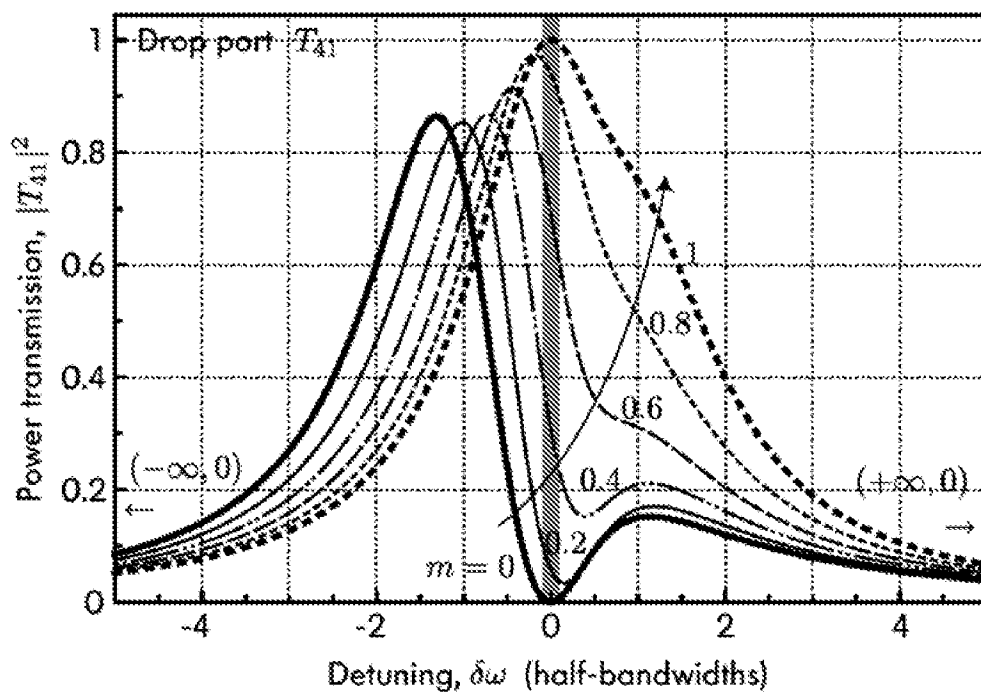


FIG. 11B

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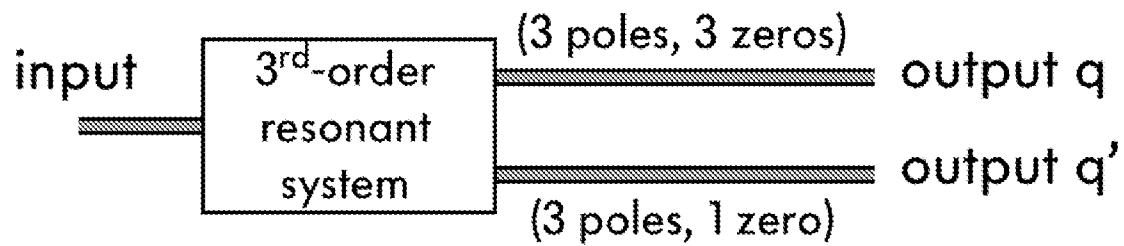


FIG. 12A

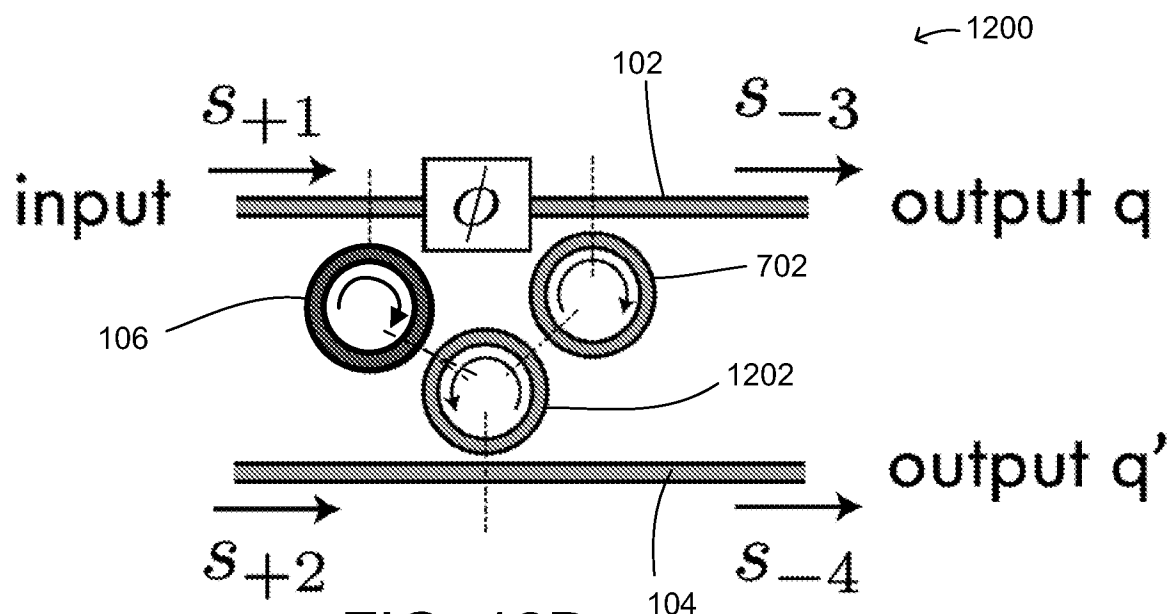
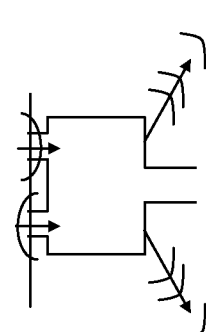
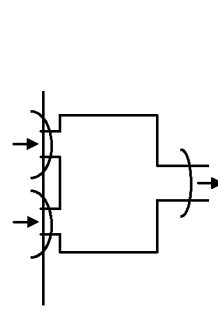
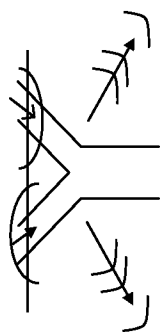
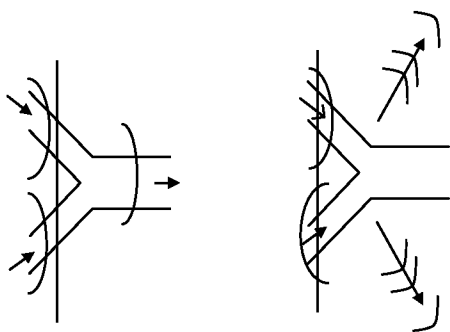
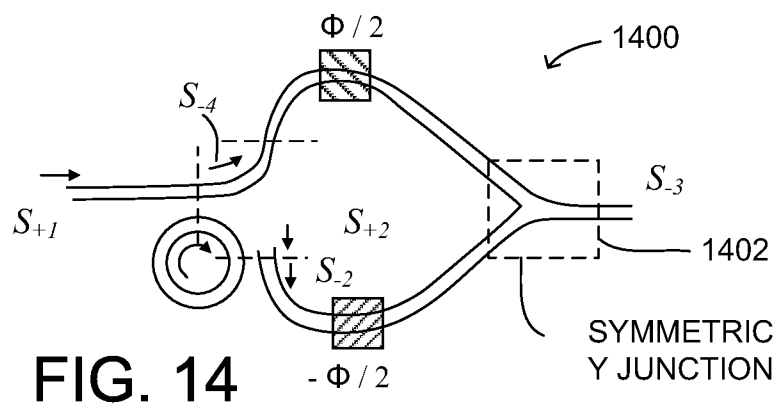
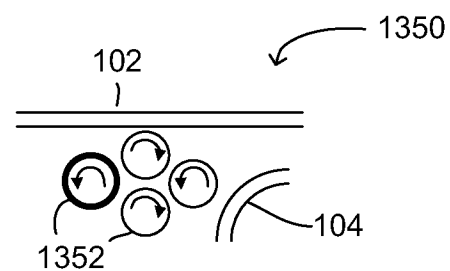
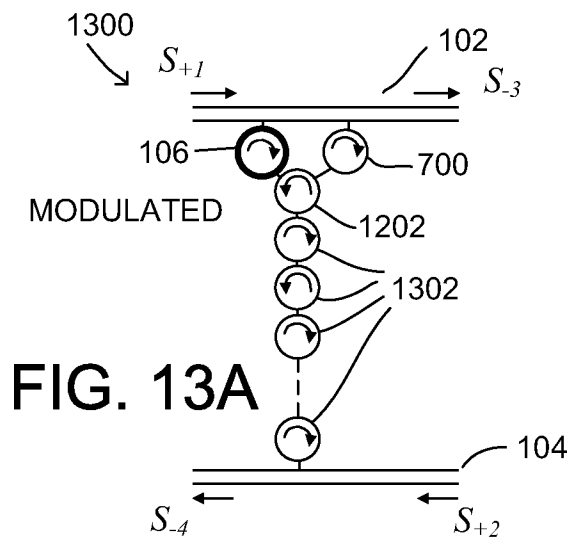


FIG. 12B



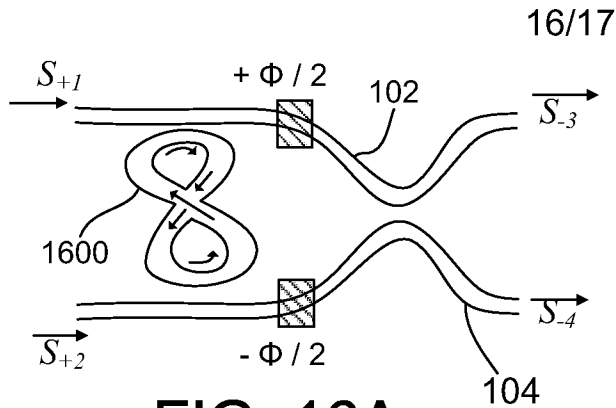


FIG. 16A

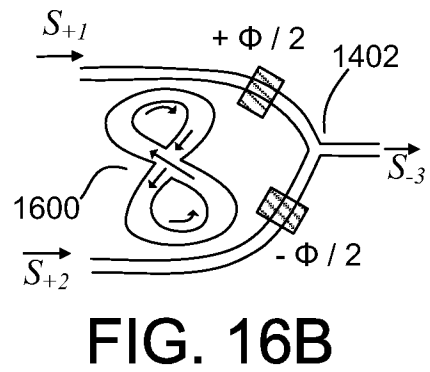


FIG. 16B

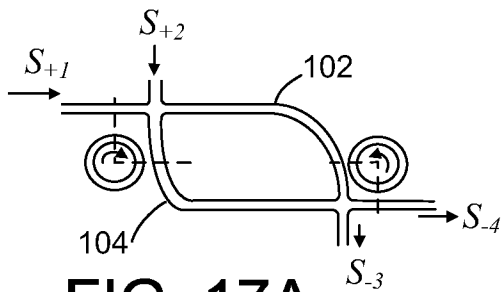


FIG. 17A

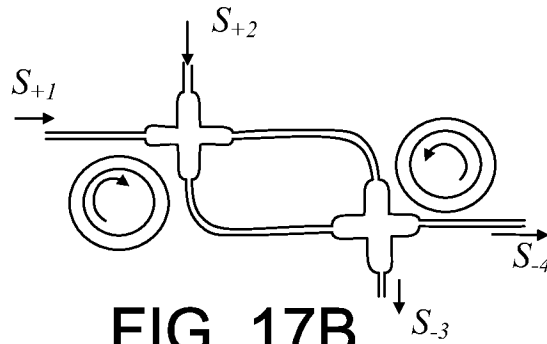


FIG. 17B

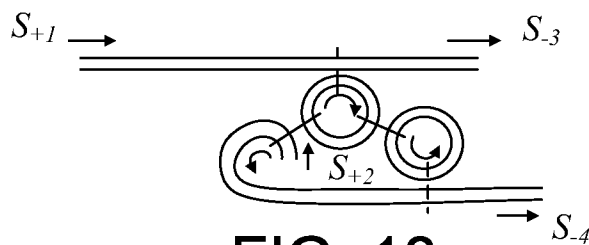


FIG. 18

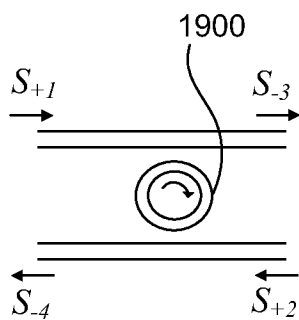


FIG. 19A

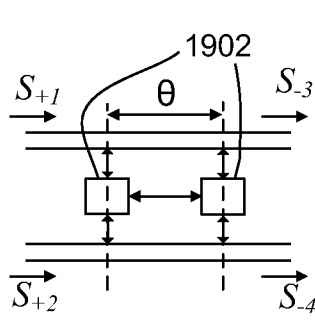


FIG. 19B

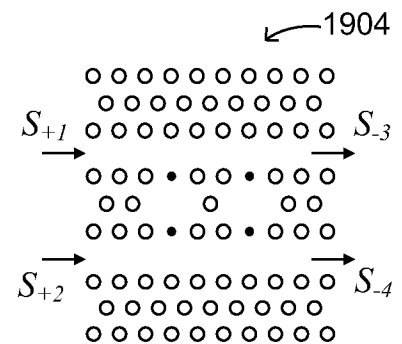
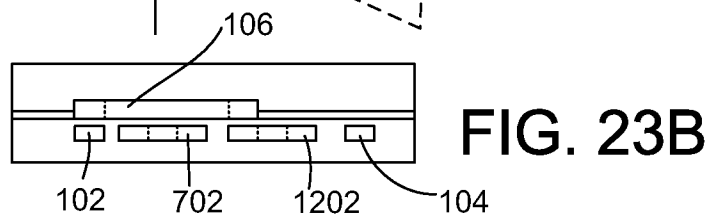
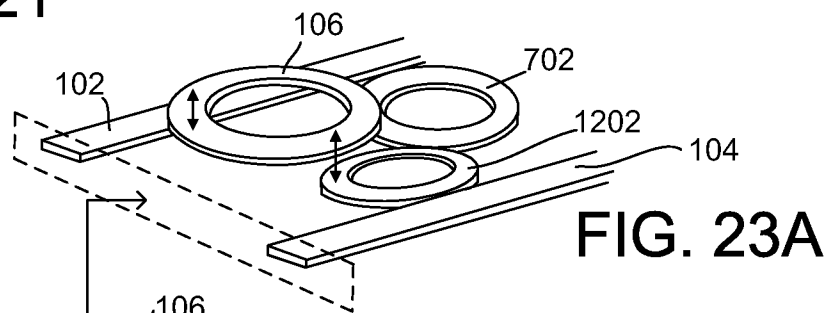
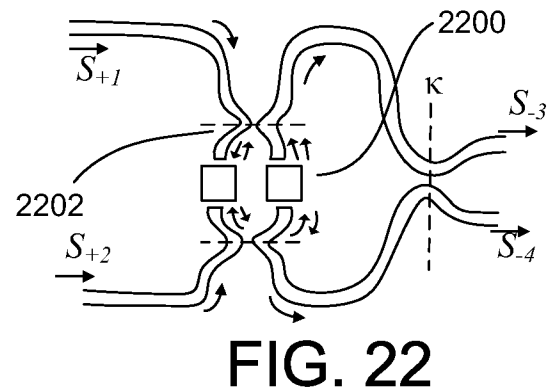
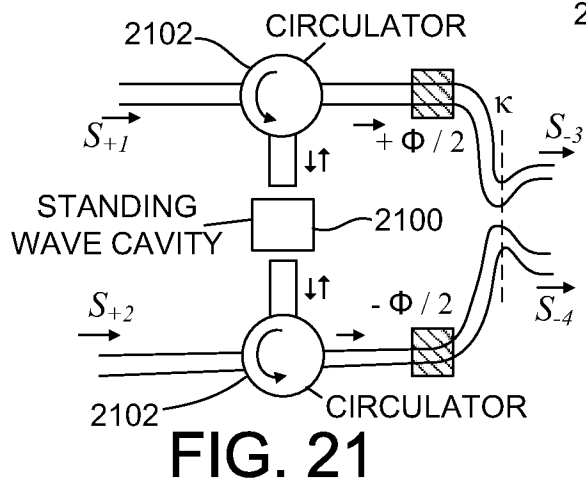
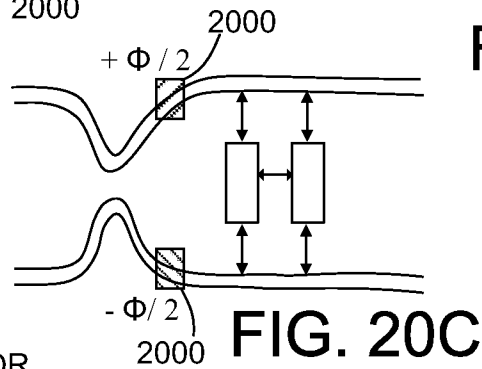
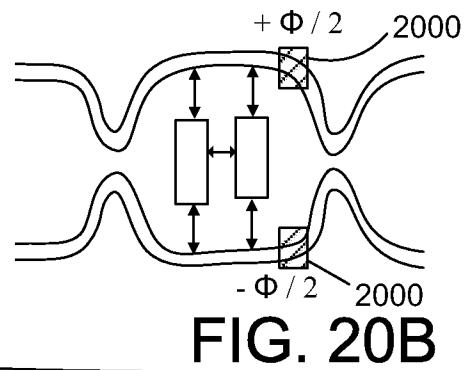
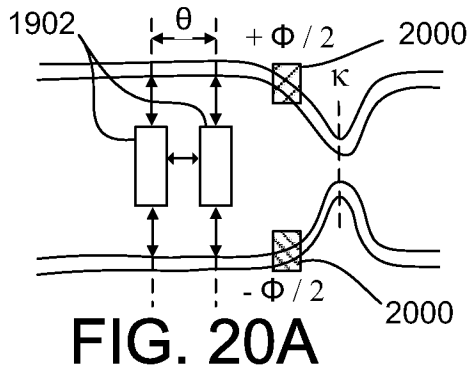


FIG. 19C

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INTERNATIONAL SEARCH REPORT

International application No
PCT/US2009/066537

A. CLASSIFICATION OF SUBJECT MATTER

INV. G02B6/12
ADD. G02F1/035

According to International Patent Classification (IPC) or to both national classification and IPC

B. FIELDS SEARCHED

Minimum documentation searched (classification system followed by classification symbols)

G02B G02F

Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched

Electronic data base consulted during the international search (name of data base and, where practical, search terms used)

EPO-Internal

C. DOCUMENTS CONSIDERED TO BE RELEVANT

Category*	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
X	WO 00/50938 A1 (MASSACHUSETTS INST TECHNOLOGY [US]) 31 August 2000 (2000-08-31)	1-3, 7, 10
Y	figures 2, 3, 7 page 13, line 14 - line 27	18
X	US 2004/161188 A1 (SU JUN [US] ET AL) 19 August 2004 (2004-08-19)	1, 3-5, 11, 17
Y	figures 1-8 paragraph [0021]	6
X	EP 1 717 616 A1 (HARRIS CORP [US]) 2 November 2006 (2006-11-02)	1, 7-9
Y	figure 16	18
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☒ Further documents are listed in the continuation of Box C.

☒ See patent family annex.

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Date of the actual completion of the international search

8 April 2010

Date of mailing of the international search report

16/04/2010

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Beutter, Matthias

INTERNATIONAL SEARCH REPORT

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PCT/US2009/066537

C(Continuation). DOCUMENTS CONSIDERED TO BE RELEVANT

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Y	figures 11-15 paragraph [0009]	6, 18
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Y	figures 3-13	18
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Y	figure 4	18
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